



2.5V/3.0V 16 Mbit Serial Quad I/O (SQI) Flash Memory

Features

- Single Voltage Read and Write Operations
 - 2.7-3.6V or 2.3-3.6V
- Serial Interface Architecture
 - Nibble-wide multiplexed I/O's with SPI-like serial command structure
 - Mode 0 and Mode 3
 - x1/x2/x4 Serial Peripheral Interface (SPI) Protocol
- High Speed Clock Frequency
 - 2.7-2.6V: 104 MHz max
 - 2.3-3.6V: 80 MHz max
- Burst Modes
 - Continuous linear burst
 - 8/16/32/64 Byte linear burst with wrap-around
- Superior Reliability
 - Endurance: 100,000 Cycles (min)
 - Greater than 100 years Data Retention
- Low Power Consumption:
 - Active Read current: 15 mA (typical @ 104 MHz)
 - Standby Current: 15 μ A (typical)
- Fast Erase Time
 - Sector/Block Erase: 18 ms (typ), 25 ms (max)
 - Chip Erase: 35 ms (typ), 50 ms (max)
- Page-Program
 - 256 Bytes per page in x1 or x4 mode
- End-of-Write Detection
 - Software polling the BUSY bit in status register
- Flexible Erase Capability
 - Uniform 4 KByte sectors
 - Four 8 KByte top and bottom parameter overlay blocks
 - One 32 KByte top and bottom overlay blocks
 - Uniform 64 KByte overlay blocks
- Write-Suspend
 - Suspend Program or Erase operation to access another block/sector
- Software Reset (RST) mode
- Software Write Protection
 - Individual-Block Write Protection with permanent lock-down capability
 - 64 KByte blocks, two 32 KByte blocks, and eight 8 KByte parameter blocks
 - Read Protection on top and bottom 8 KByte parameter blocks

- Security ID
 - One-Time Programmable (OTP) 2 KByte, Secure ID
 - 64 bit unique, factory pre-programmed identifier
 - User-programmable area
- Temperature Range
 - Industrial: -40°C to +85°C
 - Extended: -40°C to +105°C
- Packages Available
 - 8-contact WDFN (6mm x 5mm)
 - 8-lead SOIJ (5.28 mm)
 - 8-lead SOIC (3.90 mm)
- All devices are RoHS compliant

Product Description

The Serial Quad I/O™ (SQI™) family of flash-memory devices features a six-wire, 4-bit I/O interface that allows for low-power, high-performance operation in a low pin-count package. SST26VF016B also supports full command-set compatibility to traditional Serial Peripheral Interface (SPI) protocol. System designs using SQI flash devices occupy less board space and ultimately lower system costs.

All members of the 26 Series, SQI family are manufactured with proprietary, high-performance CMOS SuperFlash® technology. The split-gate cell design and thick-oxide tunneling injector attain better reliability and manufacturability compared with alternate approaches.

SST26VF016B significantly improves performance and reliability, while lowering power consumption. These devices write (Program or Erase) with a single power supply of 2.3-3.6V. The total energy consumed is a function of the applied voltage, current, and time of application. Since for any given voltage range, the SuperFlash technology uses less current to program and has a shorter erase time, the total energy consumed during any Erase or Program operation is less than alternative flash memory technologies.

SST26VF016B is offered in 8-contact WDFN (6 mm x 5 mm), 8-lead SOIJ (5.28 mm), and 8-lead SOIC (3.90 mm). See Figures 2-1 through 2-3 for pin assignments.

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1.0 BLOCK DIAGRAM

FIGURE 1-1: FUNCTIONAL BLOCK DIAGRAM



2.0 PIN DESCRIPTION

FIGURE 2-1: PIN DESCRIPTION FOR 8-LEAD SOIJ



FIGURE 2-3: PIN DESCRIPTION FOR 8-LEAD SOIC



FIGURE 2-2: PIN DESCRIPTION FOR 8-CONTACT WDFN



TABLE 2-1: PIN DESCRIPTION

| Symbol | Pin Name | Functions |
|-----------------|---------------------------------|--|
| SCK | Serial Clock | To provide the timing of the serial interface. Commands, addresses, or input data are latched on the rising edge of the clock input, while output data is shifted out on the falling edge of the clock input. |
| SIO[3:0] | Serial Data Input/Output | To transfer commands, addresses, or data serially into the device or data out of the device. Inputs are latched on the rising edge of the serial clock. Data is shifted out on the falling edge of the serial clock. The Enable Quad I/O (EQIO) command instruction configures these pins for Quad I/O mode. |
| SI | Serial Data Input for SPI mode | To transfer commands, addresses or data serially into the device. Inputs are latched on the rising edge of the serial clock. SI is the default state after a power on reset. |
| SO | Serial Data Output for SPI mode | To transfer data serially out of the device. Data is shifted out on the falling edge of the serial clock. SO is the default state after a power on reset. |
| CE# | Chip Enable | The device is enabled by a high to low transition on CE#. CE# must remain low for the duration of any command sequence; or in the case of Write operations, for the command/data input sequence. |
| WP# | Write Protect | The WP# is used in conjunction with the WPEN and IOC bits in the Configuration register to prohibit write operations to the Block-Protection register. This pin only works in SPI, single-bit and dual-bit Read mode. |
| HOLD# | Hold | Temporarily stops serial communication with the SPI Flash memory while the device is selected. This pin only works in SPI, single-bit and dual-bit Read mode and must be tied high when not in use. |
| V _{DD} | Power Supply | To provide power supply voltage. |
| V _{SS} | Ground | |

3.0 MEMORY ORGANIZATION

The SST26VF016B SQI memory array is organized in uniform, 4 KByte erasable sectors with the following erasable blocks: eight 8 KByte parameter, two 32 KByte overlay, and thirty 64 KByte overlay blocks. See Figure 3-1.

FIGURE 3-1: MEMORY MAP



4.0 DEVICE OPERATION

SST26VF016B supports both Serial Peripheral Interface (SPI) bus protocol and a 4-bit multiplexed SQI bus protocol. To provide backward compatibility to traditional SPI Serial Flash devices, the device's initial state after a power-on reset is SPI mode which supports multi-I/O (x1/x2/x4) Read/Write commands. A command instruction configures the device to SQI mode. The dataflow in the SQI mode is similar to the SPI mode, except it uses four multiplexed I/O signals for command, address, and data sequence.

SQI Flash Memory supports both Mode 0 (0,0) and Mode 3 (1,1) bus operations. The difference between the two modes is the state of the SCK signal when the

bus master is in stand-by mode and no data is being transferred. The SCK signal is low for Mode 0 and SCK signal is high for Mode 3. For both modes, the Serial Data I/O (SIO[3:0]) is sampled at the rising edge of the SCK clock signal for input, and driven after the falling edge of the SCK clock signal for output. The traditional SPI protocol uses separate input (SI) and output (SO) data signals as shown in Figure 4-1. The SQI protocol uses four multiplexed signals, SIO[3:0], for both data in and data out, as shown in Figure 4-2. This means the SQI protocol quadruples the traditional bus transfer speed at the same clock frequency, without the need for more pins on the package.

FIGURE 4-1: SPI PROTOCOL (TRADITIONAL 25 SERIES SPI DEVICE)

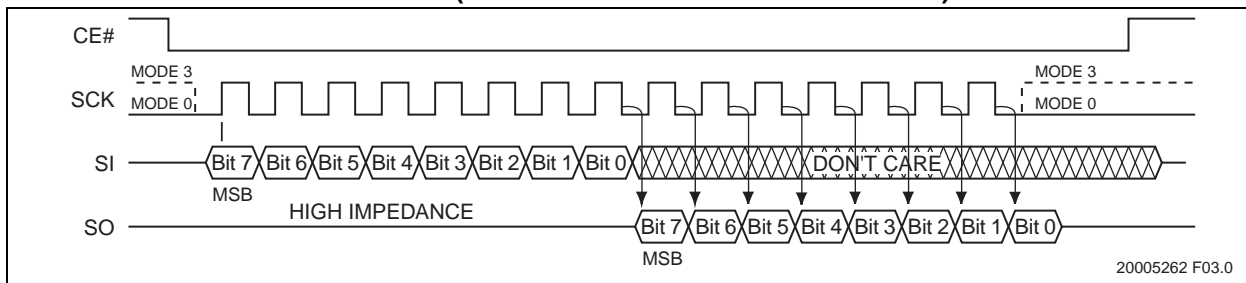


FIGURE 4-2: SQI SERIAL QUAD I/O PROTOCOL



4.1 Device Protection

SST26VF016B offers a flexible memory protection scheme that allows the protection state of each individual block to be controlled separately. In addition, the Write-Protection Lock-Down register prevents any change of the lock status during device operation. To avoid inadvertent writes during power-up, the device is write-protected by default after a power-on reset cycle. A Global Block-Protection Unlock command offers a single command cycle that unlocks the entire memory array for faster manufacturing throughput.

For extra protection, there is an additional non-volatile register that can permanently write-protect the Block-Protection register bits for each individual block. Each of the corresponding lock-down bits are one time programmable (OTP)—once written, they cannot be erased. Data that had been previously programmed into these blocks cannot be altered by programming or erase and is not reversible

4.1.1 INDIVIDUAL BLOCK PROTECTION

SST26VF016B has a Block-Protection register which provides a software mechanism to write-lock the individual memory blocks and write-lock, and/or read-lock, the individual parameter blocks. The Block-Protection register is 48 bits wide: two bits each for the eight 8 KByte parameter blocks (write-lock and read-lock), and one bit each for the remaining 32 KByte and 64 KByte overlay blocks (write-lock). See Table 5-6 for address range protected per register bit.

Each bit in the Block-Protection register (BPR) can be written to a '1' (protected) or '0' (unprotected). For the parameter blocks, the most significant bit is for read-lock, and the least significant bit is for write-lock. Read-locking the parameter blocks provides additional security for sensitive data after retrieval (e.g., after initial boot). If a block is read-locked all reads to the block return data 00H.

The Write Block-Protection Register command is a two-cycle command which requires that Write-Enable (WREN) is executed prior to the Write Block-Protection Register command. The Global Block-Protection Unlock command clears all write protection bits in the Block-Protection register.

4.1.2 WRITE-PROTECTION LOCK-DOWN (VOLATILE)

To prevent changes to the Block-Protection register, use the Lock-Down Block-Protection Register (LBPR) command to enable Write-Protection Lock-Down. Once Write-Protection Lock-Down is enabled, the Block-Protection register can not be changed. To avoid inadvertent lock down, the WREN command must be executed prior to the LBPR command.

To reset Write-Protection Lock-Down, performing a power cycle on the device is required. The Write-Protection Lock-Down status may be read from the Status register.

4.1.3 WRITE-LOCK LOCK-DOWN (NON-VOLATILE)

The non-Volatile Write-Lock Lock-Down register is an alternate register that permanently prevents changes to the block-protect bits. The non-Volatile Write-Lock Lock-Down register (nVWLDR) is 40 bits wide per device: one bit each for the eight 8-KByte parameter blocks, and one bit each for the remaining 32 KByte and 64 KByte overlay blocks. See [Table 5-6](#) for address range protected per register bit.

Writing '1' to any or all of the nVWLDR bits disables the change mechanism for the corresponding Write-Lock bit in the BPR, and permanently sets this bit to a '1' (protected) state. After this change, both bits will be set to '1', regardless of the data entered in subsequent writes to either the nVWLDR or the BPR. Subsequent writes to the nVWLDR can only alter available locations that have not been previously written to a '1'. This method provides write-protection for the corresponding memory-array block by protecting it from future program or erase operations.

Writing a '0' in any location in the nVWLDR has no effect on either the nVWLDR or the corresponding Write-Lock bit in the BPR.

Note that if the Block-Protection register had been previously locked down, see "Write-Protection Lock-Down (Volatile)", the device must be power cycled before using the nVWLDR. If the Block-Protection register is locked down and the Write nVWLDR command is accessed, the command will be ignored.

4.2 Hardware Write Protection

The hardware Write Protection pin (WP#) is used in conjunction with the WPEN and IOC bits in the configuration register to prohibit write operations to the Block-Protection and Configuration registers. The WP# pin function only works in SPI single-bit and dual-bit read mode when the IOC bit in the configuration register is set to '0'.

The WP# pin function is disabled when the WPEN bit in the configuration register is '0'. This allows installation of SST26VF016B in a system with a grounded WP# pin while still enabling Write to the Block-Protection Register. The Lock-Down function of the Block-Protection Register supersedes the WP# pin, see [Table 4-1](#) for Write Protection Lock-Down states.

The factory default setting at power-up of the WPEN bit is '0', disabling the Write Protect function of the WP# after power-up. WPEN is a non-volatile bit; once the bit is set to '1', the Write Protect function of the WP# pin continues to be enabled after power-up. The WP# pin only protects the Block-Protection Register and Configuration Register from changes. Therefore, if the WP# pin is set to low before or after a Program or Erase command, or while an internal Write is in progress, it will have no effect on the Write command.

The IOC bit takes priority over the WPEN bit in the configuration register. When the IOC bit is '1', the function of the WP# pin is disabled and the WPEN bit serves no function. When the IOC bit is '0' and WPEN is '1', setting the WP# pin active low prohibits Write operations to the Block Protection Register.

TABLE 4-1: WRITE PROTECTION LOCK-DOWN STATES

| WP# | IOC | WPEN | WPLD | Execute WBPR Instruction | Configuration Register |
|-----|----------------|----------------|------|--------------------------|------------------------|
| L | 0 | 1 | 1 | Not Allowed | Protected |
| L | 0 | 0 | 1 | Not Allowed | Writable |
| L | 0 | 1 | 0 | Not Allowed | Protected |
| L | 0 ¹ | 0 ² | 0 | Allowed | Writable |
| H | 0 | X | 1 | Not Allowed | Writable |
| H | 0 | X | 0 | Allowed | Writable |
| X | 1 | X | 1 | Not Allowed | Writable |
| X | 1 | 0 ² | 0 | Allowed | Writable |

1. Default at power-up Register settings

2. Factory default setting is '0'. This is a non-volatile bit; default at power-up is the value set prior to power-down.

4.3 Security ID

SST26VF016B offers a 2 KByte Security ID (Sec ID) feature. The Security ID space is divided into two parts – one factory-programmed, 64-bit segment and one user-programmable segment. The factory-programmed segment is programmed during part manufacture with a unique number and cannot be changed. The user-programmable segment is left unprogrammed for the customer to program as desired.

Use the Program Security ID (PSID) command to program the Security ID using the address shown in [Table 5-5](#). The Security ID can be locked using the Lockout Security ID (LSID) command. This prevents any future write operations to the Security ID.

The factory-programmed portion of the Security ID can't be programmed by the user; neither the factory-programmed nor user-programmable areas can be erased.

4.4 Hold Operation

The HOLD# pin pauses active serial sequences without resetting the clocking sequence. **This pin is active after every power up and only operates during SPI single-bit and dual-bit modes.** SST26VF016B ships

with the IOC bit set to '0' and the HOLD# pin function enabled. The HOLD# pin is always disabled in SQI mode and only works in SPI single-bit and dual-bit read mode.

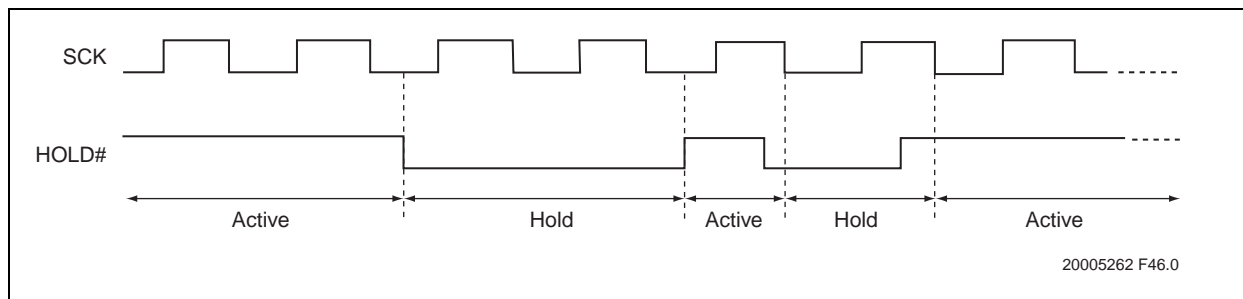
To activate the Hold mode, CE# must be in active low state. The Hold mode begins when the SCK active low state coincides with the falling edge of the HOLD# signal. The Hold mode ends when the HOLD# signal's rising edge coincides with the SCK active low state.

If the falling edge of the HOLD# signal does not coincide with the SCK active low state, then the device enters Hold mode when the SCK next reaches the active low state. Similarly, if the rising edge of the HOLD# signal does not coincide with the SCK active low state, then the device exits Hold mode when the SCK next reaches the active low state. See [Figure 4-3](#).

Once the device enters Hold mode, SO will be in high impedance state while SI and SCK can be VIL or VIH.

If CE# is driven active high during a Hold condition, it resets the internal logic of the device. As long as HOLD# signal is low, the memory remains in the Hold condition. To resume communication with the device, HOLD# must be driven active high, and CE# must be driven active low.

FIGURE 4-3: HOLD CONDITION WAVEFORM.



4.5 Status Register

The Status register is a read-only register that provides the following status information: whether the flash memory array is available for any Read or Write operation, if the device is write-enabled, whether an erase or program operation is suspended, and if the Block-

Protection register and/or Security ID are locked down. During an internal Erase or Program operation, the Status register may be read to determine the completion of an operation in progress. [Table 4-2](#) describes the function of each bit in the Status register.

TABLE 4-2: STATUS REGISTER

| Bit | Name | Function | Default at Power-up | Read/Write (R/W) |
|-----|------------------|---|---------------------|------------------|
| 0 | BUSY | Write operation status 1 = Internal Write operation is in progress 0 = No internal Write operation is in progress | 0 | R |
| 1 | WEL | Write-Enable Latch status 1 = Device is write-enabled 0 = Device is not write-enabled | 0 | R |
| 2 | WSE | Write Suspend-Erase status 1 = Erase suspended 0 = Erase is not suspended | 0 | R |
| 3 | WSP | Write Suspend-Program status 1 = Program suspended 0 = Program is not suspended | 0 | R |
| 4 | WPLD | Write Protection Lock-Down status 1 = Write Protection Lock-Down enabled 0 = Write Protection Lock-Down disabled | 0 | R |
| 5 | SEC ¹ | Security ID status 1 = Security ID space locked 0 = Security ID space not locked | 0 ¹ | R |
| 6 | RES | Reserved for future use | 0 | R |
| 7 | BUSY | Write operation status 1 = Internal Write operation is in progress 0 = No internal Write operation is in progress | 0 | R |

1. The Security ID status will always be '1' at power-up after a successful execution of the Lockout Security ID instruction, otherwise default at power-up is '0'.

4.5.1 WRITE-ENABLE LATCH (WEL)

The Write-Enable Latch (WEL) bit indicates the status of the internal memory's Write-Enable Latch. If the WEL bit is set to '1', the device is write enabled. If the bit is set to '0' (reset), the device is not write enabled and does not accept any memory Program or Erase, Protection Register Write, or Lock-Down commands. The Write-Enable Latch bit is automatically reset under the following conditions:

- Power-up
- Reset
- Write-Disable (WRDI) instruction
- Page-Program instruction completion
- Sector-Erase instruction completion
- Block-Erase instruction completion
- Chip-Erase instruction completion
- Write-Block-Protection register instruction
- Lock-Down Block-Protection register instruction
- Program Security ID instruction completion
- Lockout Security ID instruction completion
- Write-Suspend instruction
- SPI Quad Page program instruction completion
- Write Status Register

4.5.2 WRITE SUSPEND ERASE STATUS (WSE)

The Write Suspend-Erase status (WSE) indicates when an Erase operation has been suspended. The WSE bit is '1' after the host issues a suspend command during an Erase operation. Once the suspended Erase resumes, the WSE bit is reset to '0'.

4.5.3 WRITE SUSPEND PROGRAM STATUS (WSP)

The Write Suspend-Program status (WSP) bit indicates when a Program operation has been suspended. The WSP is '1' after the host issues a suspend command during the Program operation. Once the suspended Program resumes, the WSP bit is reset to '0'.

4.5.4 WRITE PROTECTION LOCK-DOWN STATUS (WPLD)

The Write Protection Lock-Down status (WPLD) bit indicates when the Block-Protection register is locked-down to prevent changes to the protection settings. The WPLD is '1' after the host issues a Lock-Down Block-Protection command. After a power cycle, the WPLD bit is reset to '0'.

4.5.5 SECURITY ID STATUS (SEC)

The Security ID Status (SEC) bit indicates when the Security ID space is locked to prevent a Write command. The SEC is '1' after the host issues a Lockout SID command. Once the host issues a Lockout SID command, the SEC bit can never be reset to '0'.

4.5.6 BUSY

The Busy bit determines whether there is an internal Erase or Program operation in progress. If the BUSY bit is '1', the device is busy with an internal Erase or Program operation. If the bit is '0', no Erase or Program operation is in progress.

4.6 Configuration Register

The Configuration register is a Read/Write register that stores a variety of configuration information. See [Table 4-3](#) for the function of each bit in the register.

TABLE 4-3: CONFIGURATION REGISTER

| Bit | Name | Function | Default at Power-up | Read/Write (R/W) |
|-----|------|---|---------------------|------------------|
| 0 | RES | Reserved | 0 | R |
| 1 | IOC | I/O Configuration for SPI Mode 1 = WP# and HOLD# pins disabled 0 = WP# and HOLD# pins enabled | 0 ¹ | R/W |
| 2 | RES | Reserved | 0 | R |
| 3 | BPNV | Block-Protection Volatility State 1 = No memory block has been permanently locked 0 = Any block has been permanently locked | 1 | R |
| 4 | RES | Reserved | 0 | R |
| 5 | RES | Reserved | 0 | R |
| 6 | RES | Reserved | 0 | R |
| 7 | WPEN | Write-Protection Pin (WP#) Enable 1 = WP# enabled 0 = WP# disabled | 0 ² | R/W |

1. Default at Power-up is '0'

2. Factory default setting. This is a non-volatile bit; default at power-up will be the setting prior to power-down.

4.6.1 I/O CONFIGURATION (IOC)

The I/O Configuration (IOC) bit re-configures the I/O pins. The IOC bit is set by writing a '1' to Bit 1 of the Configuration register. When IOC bit is '0' the WP# pin and HOLD# pin are enabled (SPI or Dual Configuration setup). When IOC bit is set to '1' the SIO2 pin and SIO3 pin are enabled (SPI Quad I/O Configuration setup). The IOC bit must be set to '1' before issuing the following SPI commands: SQOR (6BH), SQIOR (EBH), RBSPI (ECH), and SPI Quad page program (32H). Without setting the IOC bit to '1', those SPI commands are not valid. The I/O configuration bit does not apply when in SQL mode. The default at power-up is '0'.

4.6.2 BLOCK-PROTECTION VOLATILITY STATE (BPNV)

The Block-Protection Volatility State bit indicates whether any block has been permanently locked with the non-Volatile Write-Lock Lock-Down register (nVWLDR). When no bits in the nVWLDR have been set, the BPNV is '1'; this is the default state from the factory. When one or more bits in the nVWLDR are set to '1', the BPNV bit will be '0' from that point forward, even after power-up.

4.6.3 WRITE-PROTECT ENABLE (WPEN)

The Write-Protect Enable (WPEN) bit is a non-volatile bit that enables the WP# pin.

The Write-Protect (WP#) pin and the Write-Protect Enable (WPEN) bit control the programmable hardware write-protect feature. Setting the WP# pin to low, and the WPEN bit to '1', enables Hardware write-protection. To disable Hardware write protection, set either the WP# pin to high or the WPEN bit to '0'. There is latency associated with writing to the WPEN bit. Poll the BUSY bit in the Status register, or wait T_{WPEN} , for the completion of the internal, self-timed Write operation. When the chip is hardware write protected, only Write operations to Block-Protection and Configuration registers are disabled. See ["Hardware Write Protection" on page 7](#) and [Table 4-1 on page 7](#) for more information about the functionality of the WPEN bit.

5.0 INSTRUCTIONS

Instructions are used to read, write (erase and program), and configure the SST26VF016B. The complete list of the instructions is provided in [Table 5-1](#).

TABLE 5-1: DEVICE OPERATION INSTRUCTIONS FOR SST26VF016B

| Instruction | Description | Command Cycle ¹ | Mode | | Address Cycle(s) ^{2, 3} | Dummy Cycle(s) ³ | Data Cycle(s) ³ | Max ⁴ Freq |
|--------------------------|--|----------------------------|------|-----|----------------------------------|-----------------------------|----------------------------|-----------------------|
| | | | SPI | SQI | | | | |
| Configuration | | | | | | | | |
| NOP | No Operation | 00H | X | X | 0 | 0 | 0 | 104 MHz / 80 MHz |
| RSTEN | Reset Enable | 66H | X | X | 0 | 0 | 0 | |
| RST ⁵ | Reset Memory | 99H | X | X | 0 | 0 | 0 | |
| EQIO | Enable Quad I/O | 38H | X | | 0 | 0 | 0 | |
| RSTQIO ⁶ | Reset Quad I/O | FFH | X | X | 0 | 0 | 0 | |
| RDSR | Read Status Register | 05H | X | | 0 | 0 | 1 to ∞ | |
| | | | | X | 0 | 1 | 1 to ∞ | |
| WRSR | Write Status Register | 01H | X | X | 0 | 0 | 2 | |
| RDRCR | Read Configuration Register | 35H | X | | 0 | 0 | 1 to ∞ | |
| | | | | X | 0 | 1 | 1 to ∞ | |
| Read | | | | | | | | |
| Read | Read Memory | 03H | X | | 3 | 0 | 1 to ∞ | 40 MHz |
| High-Speed Read | Read Memory at Higher Speed | 0BH | | X | 3 | 3 | 1 to ∞ | 104 MHz / 80 MHz |
| | | | X | | 3 | 1 | 1 to ∞ | |
| SQOR ⁷ | SPI Quad Output Read | 6BH | X | | 3 | 1 | 1 to ∞ | |
| SQIOR ⁸ | SPI Quad I/O Read | EBH | X | | 3 | 3 | 1 to ∞ | |
| SDOR ⁹ | SPI Dual Output Read | 3BH | X | | 3 | 1 | 1 to ∞ | |
| SDIOR ¹⁰ | SPI Dual I/O Read | BBH | X | | 3 | 1 | 1 to ∞ | |
| SB | Set Burst Length | C0H | X | X | 0 | 0 | 1 | |
| RBSQI | SQI Read Burst with Wrap | 0CH | | X | 3 | 3 | n to ∞ | |
| RBSPI ⁸ | SPI Read Burst with Wrap | ECH | X | | 3 | 3 | n to ∞ | |
| Identification | | | | | | | | |
| JEDEC-ID | JEDEC-ID Read | 9FH | X | | 0 | 0 | 3 to ∞ | 104 MHz / 80 MHz |
| Quad J-ID | Quad I/O J-ID Read | AFH | | X | 0 | 1 | 3 to ∞ | |
| SFDP | Serial Flash Discoverable Parameters | 5AH | X | | 3 | 1 | 1 to ∞ | |
| Write | | | | | | | | |
| WREN | Write Enable | 06H | X | X | 0 | 0 | 0 | 104 MHz / 80 MHz |
| WRDI | Write Disable | 04H | X | X | 0 | 0 | 0 | |
| SE ¹¹ | Erase 4 KBytes of Memory Array | 20H | X | X | 3 | 0 | 0 | |
| BE ¹² | Erase 64, 32 or 8 KBytes of Memory Array | D8H | X | X | 3 | 0 | 0 | |
| CE | Erase Full Array | C7H | X | X | 0 | 0 | 0 | |
| PP | Page Program | 02H | X | X | 3 | 0 | 1 to 256 | |
| SPI Quad PP ⁷ | SQI Quad Page Program | 32H | X | | 3 | 0 | 1 to 256 | |

TABLE 5-1: DEVICE OPERATION INSTRUCTIONS FOR SST26VF016B

| Instruction | Description | Command Cycle ¹ | Mode | | Address Cycle(s) ^{2, 3} | Dummy Cycle(s) ³ | Data Cycle(s) ³ | Max ⁴ Freq |
|---------------------|--|----------------------------|------|-----|----------------------------------|-----------------------------|----------------------------|-----------------------|
| | | | SPI | SQI | | | | |
| WRSU | Suspends Program/Erase | B0H | X | X | 0 | 0 | 0 | 104 MHz / 80 MHz |
| WRRE | Resumes Program/Erase | 30H | X | X | 0 | 0 | 0 | |
| Protection | | | | | | | | |
| RBPR | Read Block-Protection Register | 72H | X | | 0 | 0 | 1 to 6 | 104 MHz / 80 MHz |
| | | | | X | 0 | 1 | 1 to 6 | |
| WBPR | Write Block-Protection Register | 42H | X | X | 0 | 0 | 1 to 6 | |
| LBPR | Lock Down Block-Protection Register | 8DH | X | X | 0 | 0 | 0 | |
| nVWLD | non-Volatile Write Lock-Down Register | E8H | X | X | 0 | 0 | 1 to 6 | |
| ULBPR | Global Block Protection Unlock | 98H | X | X | 0 | 0 | 0 | |
| RSID | Read Security ID | 88H | X | | 2 | 1 | 1 to 2048 | |
| | | | | X | 2 | 3 | 1 to 2048 | |
| PSID | Program User Security ID area | A5H | X | X | 2 | 0 | 1 to 256 | |
| LSID | Lockout Security ID Programming | 85H | X | X | 0 | 0 | 0 | |
| Power Saving | | | | | | | | |
| DPD | Deep Power-down Mode | B9H | X | X | 0 | 0 | 0 | 104 MHz / 80 MHz |
| RDPD | Release from Deep Power-down and Read ID | ABH | X | X | 3 | 0 | 1 to ∞ | |

1. Command cycle is two clock periods in SQI mode and eight clock periods in SPI mode.
2. Address bits above the most significant bit of each density can be V_{IL} or V_{IH}.
3. Address, Dummy/Mode bits, and Data cycles are two clock periods in SQI and eight clock periods in SPI mode.
4. The max frequency for all instructions is up to 104 MHz from 2.7-3.6V and up to 80 MHz from 2.3-3.6V unless otherwise noted.
5. RST command only executed if RSTEN command is executed first. Any intervening command will disable Reset.
6. Device accepts eight-clock command in SPI mode, or two-clock command in SQI mode.
7. Data cycles are two clock periods. IOC bit must be set to '1' before issuing the command.
8. Address, Dummy/Mode bits, and data cycles are two clock periods. IOC bit must be set to '1' before issuing the command.
9. Data cycles are four clock periods.
10. Address, Dummy/Mode bits, and Data cycles are four clock periods.
11. Sector Addresses: Use A_{MS} - A₁₂, remaining address are don't care, but must be set to V_{IL} or V_{IH}.
12. Blocks are 64 KByte, 32 KByte, or 8KByte, depending on location. Block Erase Address: A_{MS} - A₁₆ for 64 KByte; A_{MS} - A₁₅ for 32 KByte; A_{MS} - A₁₃ for 8 KByte. Remaining addresses are don't care, but must be set to V_{IL} or V_{IH}.

5.1 No Operation (NOP)

The No Operation command only cancels a Reset Enable command. NOP has no impact on any other command.

5.2 Reset-Enable (RSTEN) and Reset (RST)

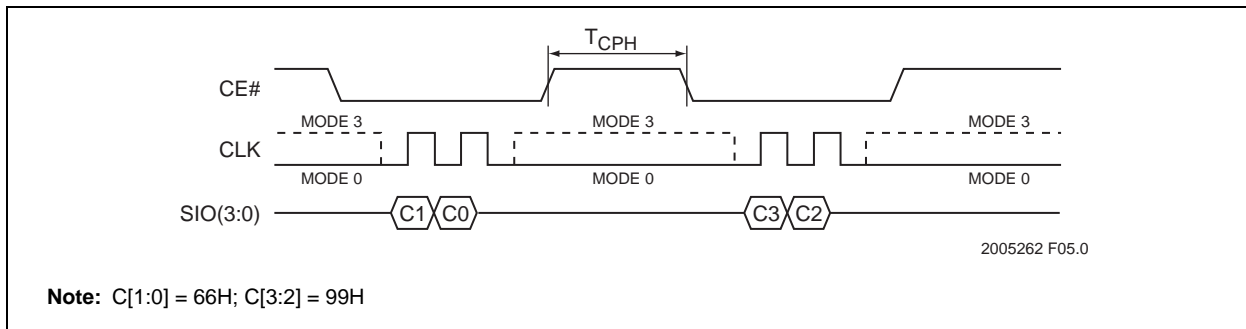
The Reset operation is used as a system (software) reset that puts the device in normal operating Ready mode. This operation consists of two commands: Reset-Enable (RSTEN) followed by Reset (RST).

To reset SST26VF016B, the host drives CE# low, sends the Reset-Enable command (66H), and drives CE# high. Next, the host drives CE# low again, sends the Reset command (99H), and drives CE# high, see Figure 5-1.

The Reset operation requires the Reset-Enable command followed by the Reset command. Any command other than the Reset command after the Reset-Enable command will disable the Reset-Enable.

Once the Reset-Enable and Reset commands are successfully executed, the device returns to normal operation Read mode and then does the following: resets the protocol to SPI mode, resets the burst length to 8 Bytes, clears all the bits, except for bit 4 (WPLD) and bit 5 (SEC), in the Status register to their default states, and clears bit 1 (IOC) in the configuration register to its default state. A device reset during an active Program or Erase operation aborts the operation, which can cause the data of the targeted address range to be corrupted or lost. Depending on the prior operation, the reset timing may vary. Recovery from a Write operation requires more latency time than recovery from other operations. See Table 8-2 on page 46 for Rest timing parameters.

FIGURE 5-1: RESET SEQUENCE



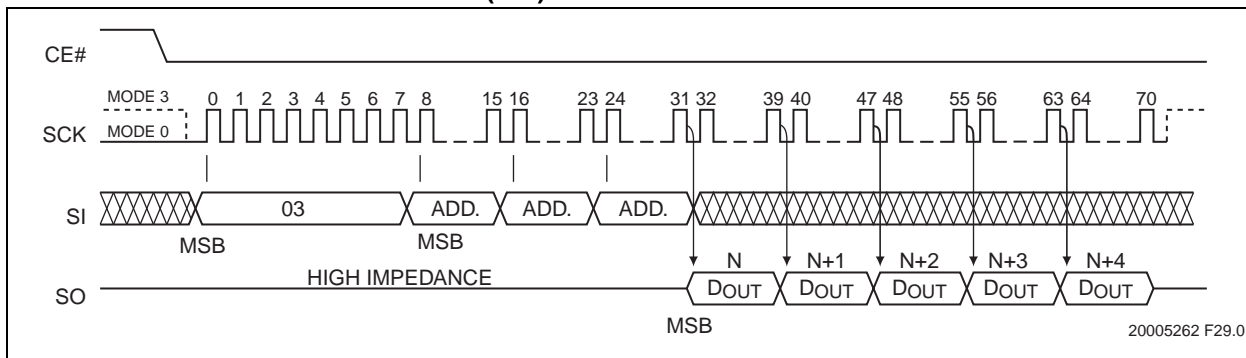
5.3 Read (40 MHz)

The Read instruction, 03H, is supported in SPI bus protocol only with clock frequencies up to 40 MHz. This command is not supported in SQI bus protocol. The device outputs the data starting from the specified address location, then continuously streams the data output through all addresses until terminated by a low-to-high transition on CE#. The internal address pointer

will automatically increment until the highest memory address is reached. Once the highest memory address is reached, the address pointer will automatically return to the beginning (wrap-around) of the address space.

Initiate the Read instruction by executing an 8-bit command, 03H, followed by address bits A[23:0]. CE# must remain active low for the duration of the Read cycle. See Figure 5-2 for Read Sequence.

FIGURE 5-2: READ SEQUENCE (SPI)

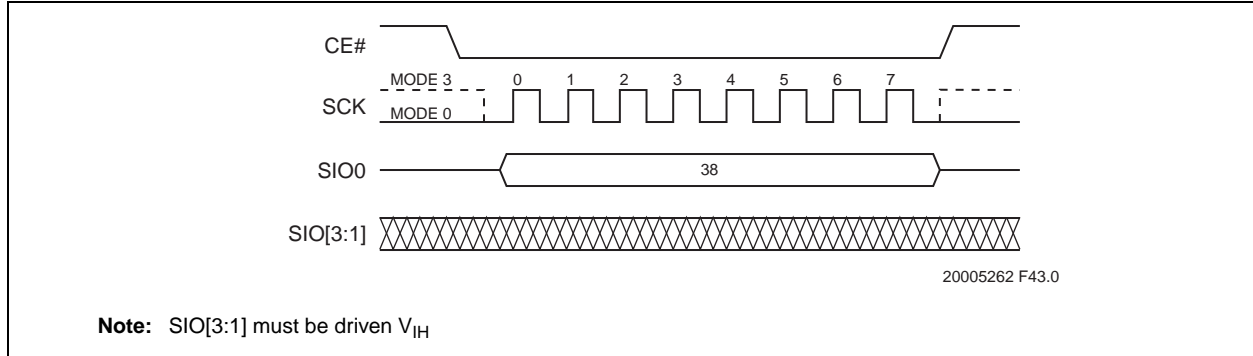


5.4 Enable Quad I/O (EQIO)

The Enable Quad I/O (EQIO) instruction, 38H, enables the flash device for SQI bus operation. Upon completion of the instruction, all instructions thereafter are

expected to be 4-bit multiplexed input/output (SQI mode) until a power cycle or a “Reset Quad I/O instruction” is executed. See [Figure 5-3](#).

FIGURE 5-3: ENABLE QUAD I/O SEQUENCE



5.5 Reset Quad I/O (RSTQIO)

The Reset Quad I/O instruction, FFH, resets the device to 1-bit SPI protocol operation or exits the Set Mode configuration during a read sequence. This command allows the flash device to return to the default I/O state (SPI) without a power cycle, and executes in either 1-bit or 4-bit mode. If the device is in the Set Mode configuration, while in SQI High-Speed Read mode, the RSTQIO command will only return the device to a state

where it can accept new command instruction. An additional RSTQIO is required to reset the device to SPI mode.

To execute a Reset Quad I/O operation, the host drives CE# low, sends the Reset Quad I/O command cycle (FFH) then, drives CE# high. Execute the instruction in either SPI (8 clocks) or SQI (2 clocks) command cycles. For SPI, SIO[3:1] are don't care for this command, but should be driven to V_{IH} or V_{IL} . See [Figures 5-4](#) and [5-5](#).

FIGURE 5-4: RESET QUAD I/O SEQUENCE (SPI)

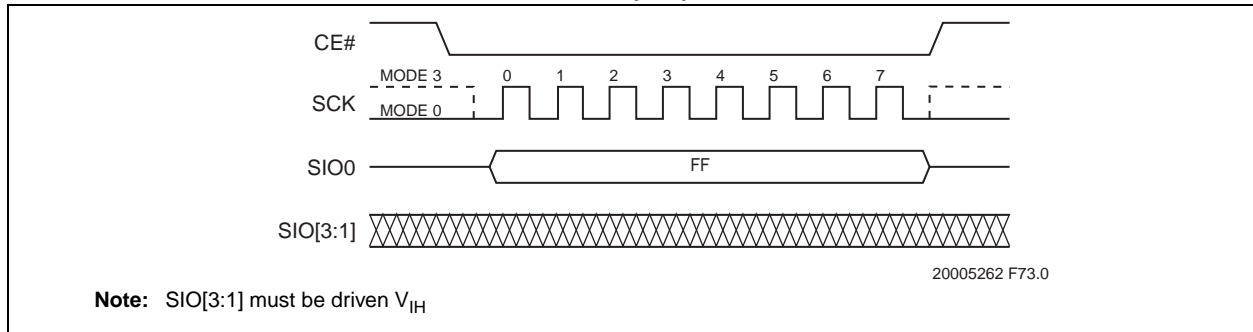
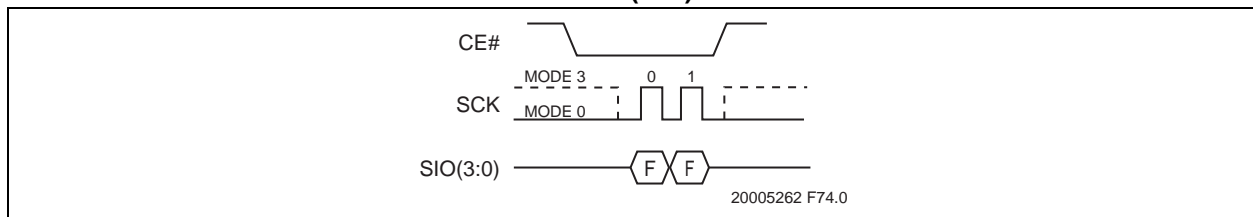


FIGURE 5-5: RESET QUAD I/O SEQUENCE (SQI)



5.6 High-Speed Read

The High-Speed Read instruction, 0BH, is supported in both SPI protocol and SQI protocol. This instruction supports frequencies of up to 104 MHz from 2.7-3.6V and up to 80 MHz from 2.3-3.6V. On power-up, the device is set to use SPI.

Initiate High-Speed Read by executing an 8-bit command, 0BH, followed by address bits A[23:0] and a dummy byte. CE# must remain active low for the duration of the High-Speed Read cycle. See Figure 5-6 for the High-Speed Read sequence for SPI bus protocol.

FIGURE 5-6: HIGH-SPEED READ SEQUENCE (SPI) (C[1:0] = 0BH)



In SQI protocol, the host drives CE# low then sends one High-Speed Read command cycle, 0BH, followed by three address cycles, a Set Mode Configuration cycle, and two dummy cycles. Each cycle is two nibbles (clocks) long, most significant nibble first.

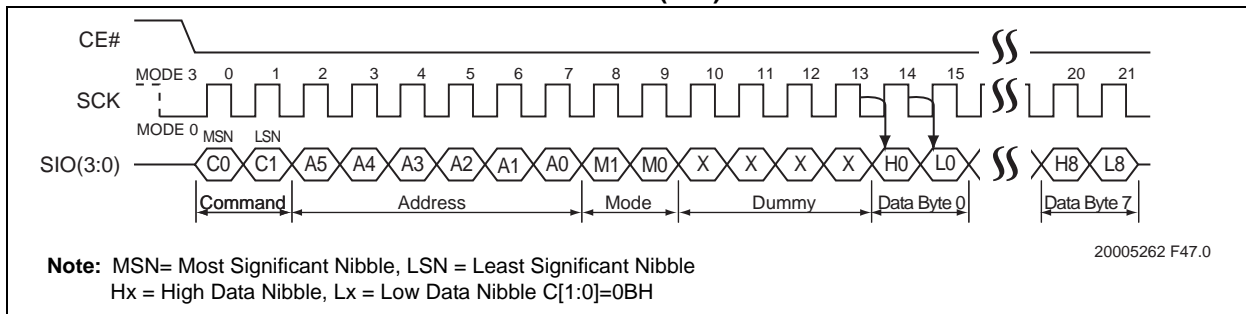
After the dummy cycles, the device outputs data on the falling edge of the SCK signal starting from the specified address location. The device continually streams data output through all addresses until terminated by a low-to-high transition on CE#. The internal address pointer automatically increments until the highest memory address is reached, at which point the address pointer returns to address location 000000H. During this operation, blocks that are Read-locked will output data 00H.

The Set Mode Configuration bit M[7:0] indicates if the next instruction cycle is another SQI High-Speed Read command. When M[7:0] = AXH, the device expects the next continuous instruction to be another Read com-

mand, 0BH, and does not require the op-code to be entered again. The host may initiate the next Read cycle by driving CE# low, then sending the four-bits input for address A[23:0], followed by the Set Mode configuration bits M[7:0], and two dummy cycles. After the two dummy cycles, the device outputs the data starting from the specified address location. There are no restrictions on address location access.

When M[7:0] is any value other than AXH, the device expects the next instruction initiated to be a command instruction. To reset/exit the Set Mode configuration, execute the Reset Quad I/O command, FFH. While in the Set Mode configuration, the RSTQIO command will only return the device to a state where it can accept new command instruction. An additional RSTQIO is required to reset the device to SPI mode. See Figure 5-10 for the SPI Quad I/O Mode Read sequence when M[7:0] = AXH.

FIGURE 5-7: HIGH-SPEED READ SEQUENCE (SQI)



5.7 SPI Quad-Output Read

The SPI Quad-Output Read instruction supports frequencies of up to 104 MHz from 2.7-3.6V and up to 80 MHz from 2.3-3.6V. SST26VF016B requires the IOC bit in the configuration register to be set to '1' prior to executing the command. Initiate SPI Quad-Output Read by executing an 8-bit command, 6BH, followed by address bits A[23:0] and a dummy byte. CE# must remain active low for the duration of the SPI Quad Mode Read. See Figure 5-8 for the SPI Quad Output Read sequence.

Following the dummy byte, the device outputs data from SIO[3:0] starting from the specified address location. The device continually streams data output through all addresses until terminated by a low-to-high transition on CE#. The internal address pointer automatically increments until the highest memory address is reached, at which point the address pointer returns to the beginning of the address space.

FIGURE 5-8: SPI QUAD OUTPUT READ



5.8 SPI Quad I/O Read

The SPI Quad I/O Read (SQIOR) instruction supports frequencies of up to 104 MHz from 2.7-3.6V and up to 80 MHz from 2.3-3.6V. SST26VF016B requires the IOC bit in the configuration register to be set to '1' prior to executing the command. Initiate SQIOR by executing an 8-bit command, EBH. The device then switches to 4-bit I/O mode for address bits A[23:0], followed by the Set Mode configuration bits M[7:0], and two dummy bytes. CE# must remain active low for the duration of the SPI Quad I/O Read. See Figure 5-9 for the SPI Quad I/O Read sequence.

Following the dummy bytes, the device outputs data from the specified address location. The device continually streams data output through all addresses until terminated by a low-to-high transition on CE#. The internal address pointer automatically increments until the highest memory address is reached, at which point the address pointer returns to the beginning of the address space.

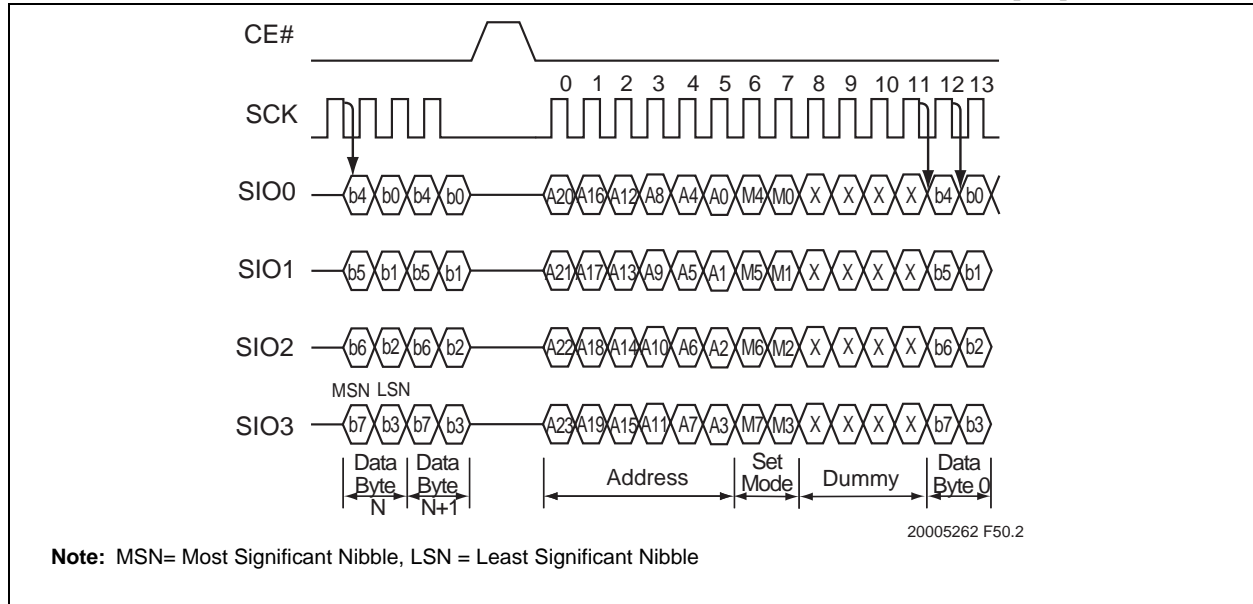
The Set Mode Configuration bit M[7:0] indicates if the next instruction cycle is another SPI Quad I/O Read command. When M[7:0] = AXH, the device expects the next continuous instruction to be another Read command, EBH, and does not require the op-code to be entered again. The host may set the next SQIOR cycle by driving CE# low, then sending the four-bit wide input for address A[23:0], followed by the Set Mode configuration bits M[7:0], and two dummy cycles. After the two dummy cycles, the device outputs the data starting from the specified address location. There are no restrictions on address location access.

When M[7:0] is any value other than AXH, the device expects the next instruction initiated to be a command instruction. To reset/exit the Set Mode configuration, execute the Reset Quad I/O command, FFH. See Figure 5-10 for the SPI Quad I/O Mode Read sequence when M[7:0] = AXH.

FIGURE 5-9: SPI QUAD I/O READ SEQUENCE



FIGURE 5-10: BACK-TO-BACK SPI QUAD I/O READ SEQUENCES WHEN M[7:0] = AXH



5.9 Set Burst

The Set Burst command specifies the number of bytes to be output during a Read Burst command before the device wraps around. It supports both SPI and SQI protocols. To set the burst length the host drives CE# low,

sends the Set Burst command cycle (C0H) and one data cycle, then drives CE# high. After power-up or reset, the burst length is set to eight Bytes (00H). See [Table 5-2](#) for burst length data and [Figures 5-11](#) and [5-12](#) for the sequences.

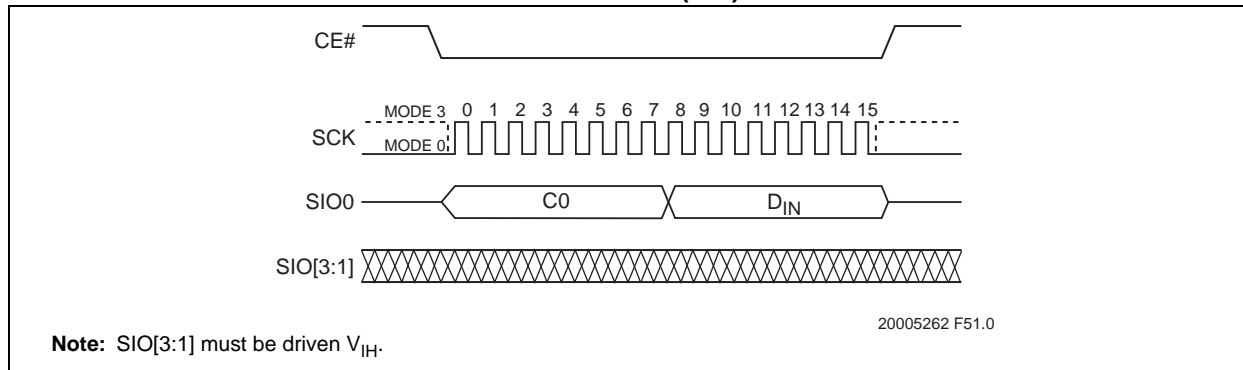
TABLE 5-2: BURST LENGTH DATA

| Burst Length | High Nibble (H0) | Low Nibble (L0) |
|--------------|------------------|-----------------|
| 8 Bytes | 0h | 0h |
| 16 Bytes | 0h | 1h |
| 32 Bytes | 0h | 2h |
| 64 Bytes | 0h | 3h |

FIGURE 5-11: SET BURST LENGTH SEQUENCE (SQI)



FIGURE 5-12: SET BURST LENGTH SEQUENCE (SPI)



5.10 SQI Read Burst with Wrap (RBSQI)

SQI Read Burst with wrap is similar to High Speed Read in SQI mode, except data will output continuously within the burst length until a low-to-high transition on CE#. To execute a SQI Read Burst operation, drive CE# low then send the Read Burst command cycle (0CH), followed by three address cycles, and then three dummy cycles. Each cycle is two nibbles (clocks) long, most significant nibble first.

After the dummy cycles, the device outputs data on the falling edge of the SCK signal starting from the specified address location. The data output stream is continuous through all addresses until terminated by a low-to-high transition on CE#.

During RBSQI, the internal address pointer automatically increments until the last byte of the burst is reached, then it wraps around to the first byte of the burst. All bursts are aligned to addresses within the burst length, see Table 5-3. For example, if the burst length is eight Bytes, and the start address is 06h, the burst sequence would be: 06h, 07h, 00h, 01h, 02h, 03h, 04h, 05h, 06h, etc. The pattern repeats until the command is terminated by a low-to-high transition on CE#.

During this operation, blocks that are Read-locked will output data 00H.

5.11 SPI Read Burst with Wrap (RBSPI)

SPI Read Burst with Wrap (RBSPI) is similar to SPI Quad I/O Read except the data will output continuously within the burst length until a low-to-high transition on CE#. To execute a SPI Read Burst with Wrap operation, drive CE# low, then send the Read Burst command cycle (ECH), followed by three address cycles, and then three dummy cycles.

After the dummy cycle, the device outputs data on the falling edge of the SCK signal starting from the specified address location. The data output stream is continuous through all addresses until terminated by a low-to-high transition on CE#.

During RBSPI, the internal address pointer automatically increments until the last byte of the burst is reached, then it wraps around to the first byte of the burst. All bursts are aligned to addresses within the burst length, see Table 5-3. For example, if the burst length is eight Bytes, and the start address is 06h, the burst sequence would be: 06h, 07h, 00h, 01h, 02h, 03h, 04h, 05h, 06h, etc. The pattern repeats until the command is terminated by a low-to-high transition on CE#.

During this operation, blocks that are Read-locked will output data 00H.

TABLE 5-3: BURST ADDRESS RANGES

| Burst Length | Burst Address Ranges |
|--------------|-----------------------------------|
| 8 Bytes | 00-07H, 08-0FH, 10-17H, 18-1FH... |
| 16 Bytes | 00-0FH, 10-1FH, 20-2FH, 30-3FH... |
| 32 Bytes | 00-1FH, 20-3FH, 40-5FH, 60-7FH... |
| 64 Bytes | 00-3FH, 40-7FH, 80-BFH, C0-FFH |

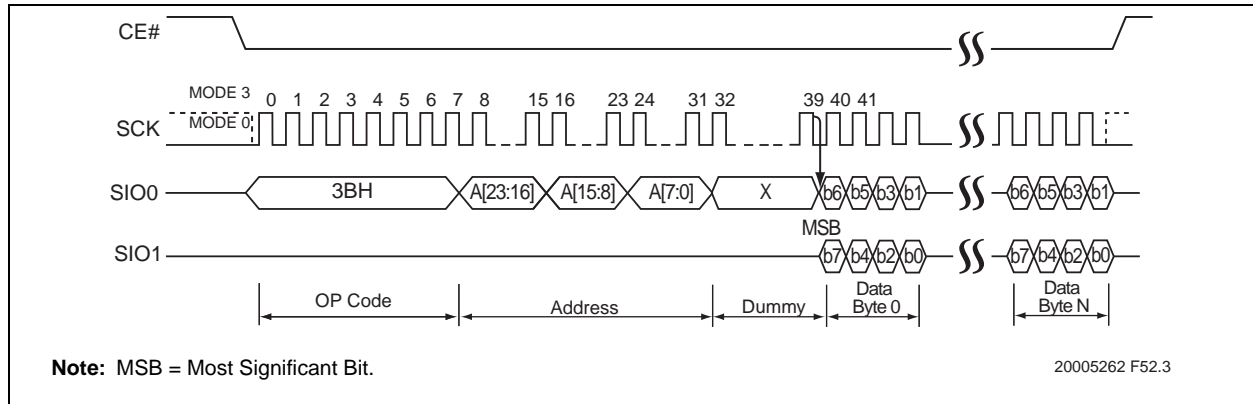
0

5.12 SPI Dual-Output Read

The SPI Dual-Output Read instruction supports frequencies of up to 104 MHz from 2.7-3.6V and up to 80 MHz from 2.3-3.6V. Initiate SPI Dual-Output Read by executing an 8-bit command, 3BH, followed by address bits A[23:0] and a dummy byte. CE# must remain active low for the duration of the SPI Dual-Output Read operation. See Figure 5-13 for the SPI Quad Output Read sequence.

Following the dummy byte, SST26VF016B outputs data from SIO[1:0] starting from the specified address location. The device continually streams data output through all addresses until terminated by a low-to-high transition on CE#. The internal address pointer automatically increments until the highest memory address is reached, at which point the address pointer returns to the beginning of the address space.

FIGURE 5-13: FAST READ, DUAL-OUTPUT SEQUENCE



5.13 SPI Dual I/O Read

The SPI Dual I/O Read (SDIOR) instruction supports up to 80 MHz frequency. Initiate SDIOR by executing an 8-bit command, BBH. The device then switches to 2-bit I/O mode for address bits A[23:0], followed by the Set Mode configuration bits M[7:0]. CE# must remain active low for the duration of the SPI Dual I/O Read. See Figure 5-14 for the SPI Dual I/O Read sequence.

execute the Reset Quad I/O command, FFH. See Figure 5-15 for the SPI Dual I/O Read sequence when M[7:0] = AXH.

Following the Set Mode configuration bits, the SST26VF016B outputs data from the specified address location. The device continually streams data output through all addresses until terminated by a low-to-high transition on CE#. The internal address pointer automatically increments until the highest memory address is reached, at which point the address pointer returns to the beginning of the address space.

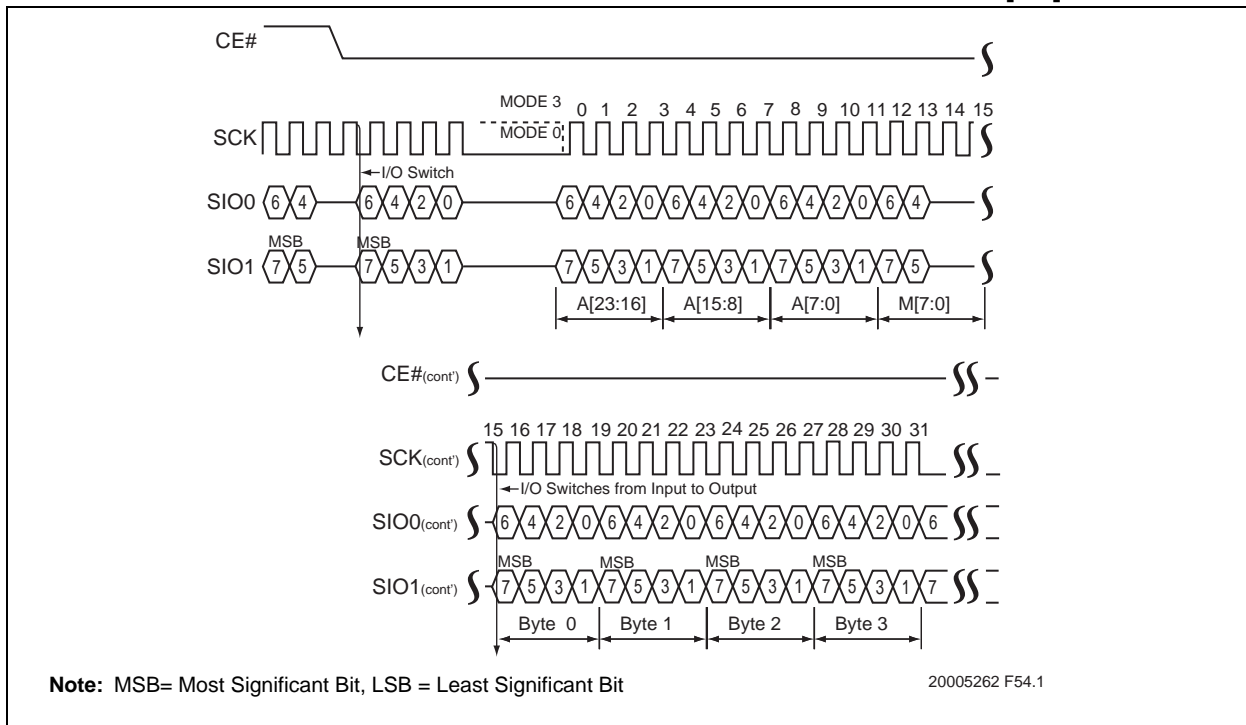
The Set Mode Configuration bit M[7:0] indicates if the next instruction cycle is another SPI Dual I/O Read command. When M[7:0] = AXH, the device expects the next continuous instruction to be another SDIOR command, BBH, and does not require the op-code to be entered again. The host may set the next SDIOR cycle by driving CE# low, then sending the two-bit wide input for address A[23:0], followed by the Set Mode configuration bits M[7:0]. After the Set Mode Configuration bits, the device outputs the data starting from the specified address location. There are no restrictions on address location access.

When M[7:0] is any value other than AXH, the device expects the next instruction initiated to be a command instruction. To reset/exit the Set Mode configuration,

FIGURE 5-14: SPI DUAL I/O READ SEQUENCE



FIGURE 5-15: BACK-TO-BACK SPI DUAL I/O READ SEQUENCES WHEN M[7:0] = AXH



5.14 JEDEC-ID Read (SPI Protocol)

Using traditional SPI protocol, the JEDEC-ID Read instruction identifies the device as SST26VF016B and the manufacturer as Microchip®. To execute a JEDEC-ID operation the host drives CE# low then sends the JEDEC-ID command cycle (9FH).

Immediately following the command cycle, SST26VF016B outputs data on the falling edge of the SCK signal. The data output stream is continuous until terminated by a low-to-high transition on CE#. The device outputs three bytes of data: manufacturer, device type, and device ID, see Table 5-4. See Figure 5-16 for instruction sequence.

TABLE 5-4: DEVICE ID DATA OUTPUT

| Product | Manufacturer ID (Byte 1) | Device ID | |
|-------------|--------------------------|----------------------|--------------------|
| | | Device Type (Byte 2) | Device ID (Byte 3) |
| SST26VF016B | BFH | 26H | 41H |

FIGURE 5-16: JEDEC-ID SEQUENCE (SPI)

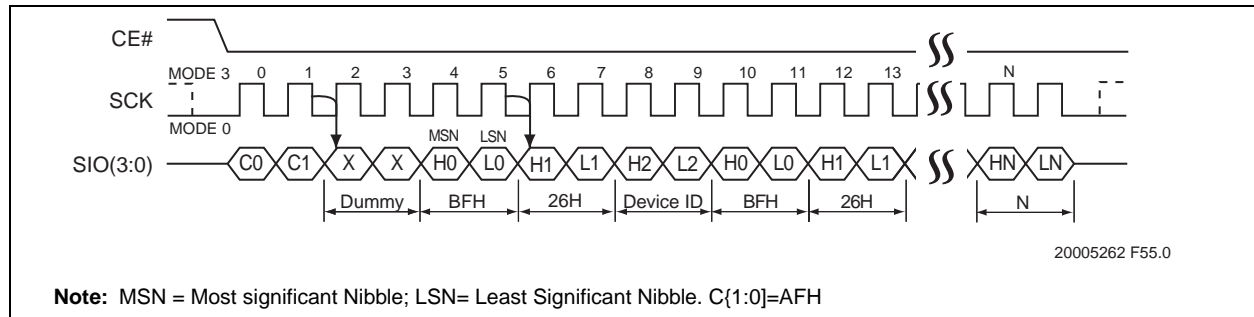


5.15 Read Quad J-ID Read (SQI Protocol)

The Read Quad J-ID Read instruction identifies the device as SST26VF016B and manufacturer as Microchip. To execute a Quad J-ID operation the host drives CE# low and then sends the Quad J-ID command cycle (AFH). Each cycle is two nibbles (clocks) long, most significant nibble first.

Immediately following the command cycle and one dummy cycle, SST26VF016B outputs data on the falling edge of the SCK signal. The data output stream is continuous until terminated by a low-to-high transition of CE#. The device outputs three bytes of data: manufacturer, device type, and device ID, see Table 5-4. See Figure 5-17 for instruction sequence.

FIGURE 5-17: QUAD J-ID READ SEQUENCE



Note: MSN = Most significant Nibble; LSN= Least Significant Nibble. C{1:0}=AFH

5.16 Serial Flash Discoverable Parameters (SFDP)

The Serial Flash Discoverable Parameters (SFDP) contain information describing the characteristics of the device. This allows device-independent, JEDEC ID-independent, and forward/backward compatible soft-

ware support for all future Serial Flash device families. See [Table 11-1 on page 58](#) for address and data values.

Initiate SFDP by executing an 8-bit command, 5AH, followed by address bits A[23-0] and a dummy byte. CE# must remain active low for the duration of the SFDP cycle. For the SFDP sequence, see [Figure 5-18](#).

FIGURE 5-18: SERIAL FLASH DISCOVERABLE PARAMETERS SEQUENCE



5.17 Sector-Erase

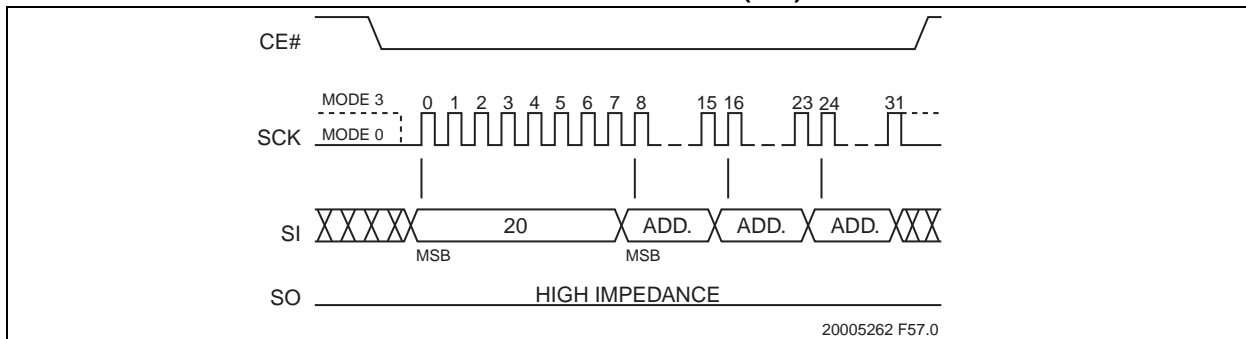
The Sector-Erase instruction clears all bits in the selected 4 KByte sector to '1,' but it does not change a protected memory area. Prior to any write operation, the Write-Enable (WREN) instruction must be executed.

To execute a Sector-Erase operation, the host drives CE# low, then sends the Sector Erase command cycle (20H) and three address cycles, and then drives CE# high. Address bits [A_{MS}:A₁₂] (A_{MS} = Most Significant Address) determine the sector address (SA_X); the remaining address bits can be V_{IL} or V_{IH}. To identify the completion of the internal, self-timed, Write operation, poll the BUSY bit in the Status register, or wait T_{SE}. See [Figures 5-19](#) and [5-20](#) for the Sector-Erase sequence.

FIGURE 5-19: 4 KBYTE SECTOR-ERASE SEQUENCE- SQI MODE



FIGURE 5-20: 4 KBYTE SECTOR-ERASE SEQUENCE (SPI)



5.18 Block-Erase

The Block-Erase instruction clears all bits in the selected block to '1'. Block sizes can be 8 KByte, 32 KByte or 64 KByte depending on address, see [Figure 3-1](#), Memory Map, for details. A Block-Erase instruction applied to a protected memory area will be ignored. Prior to any write operation, execute the WREN instruction. Keep CE# active low for the duration of any command sequence.

To execute a Block-Erase operation, the host drives CE# low then sends the Block-Erase command cycle (D8H), three address cycles, then drives CE# high. Address bits $A_{MS} - A_{13}$ determine the block address (BA_X); the remaining address bits can be V_{IL} or V_{IH} . For 32 KByte blocks, $A_{14} : A_{13}$ can be V_{IL} or V_{IH} ; for 64 KByte blocks, $A_{15} : A_{13}$ can be V_{IL} or V_{IH} . Poll the BUSY bit in the Status register, or wait T_{BE} for the completion of the internal, self-timed, Block-Erase operation. See [Figures 5-21](#) and [5-22](#) for the Block-Erase sequence.

FIGURE 5-21: BLOCK-ERASE SEQUENCE (SQI)



FIGURE 5-22: BLOCK-ERASE SEQUENCE (SPI)



5.19 Chip-Erase

The Chip-Erase instruction clears all bits in the device to '1.' The Chip-Erase instruction is ignored if any of the memory area is protected. Prior to any write operation, execute the WREN instruction.

To execute a Chip-Erase operation, the host drives CE# low, sends the Chip-Erase command cycle (C7H), then drives CE# high. Poll the BUSY bit in the Status register, or wait T_{SCE} , for the completion of the internal, self-timed, Write operation. See Figures 5-23 and 5-24 for the Chip Erase sequence.

FIGURE 5-23: CHIP-ERASE SEQUENCE (SQI)

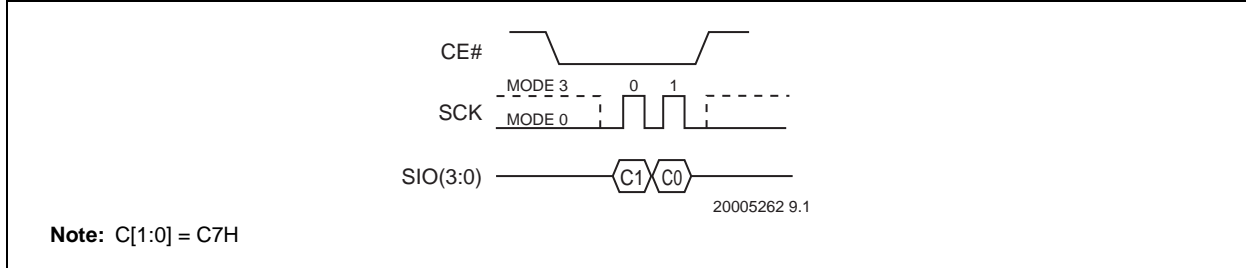
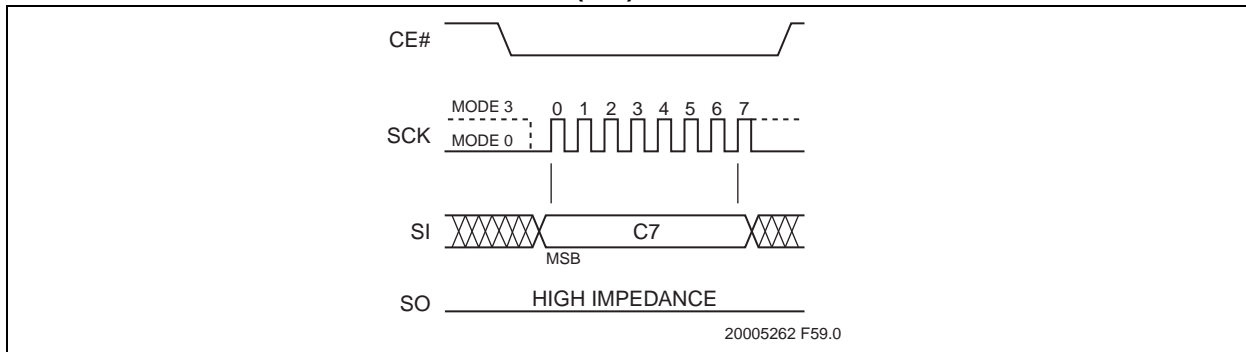


FIGURE 5-24: CHIP-ERASE SEQUENCE (SPI)



5.20 Page-Program

The Page-Program instruction programs up to 256 Bytes of data in the memory, and supports both SPI and SQI protocols. The data for the selected page address must be in the erased state (FFH) before initiating the Page-Program operation. A Page-Program applied to a protected memory area will be ignored. Prior to the program operation, execute the WREN instruction.

To execute a Page-Program operation, the host drives CE# low then sends the Page Program command cycle (02H), three address cycles followed by the data to be programmed, then drives CE# high. The programmed data must be between 1 to 256 Bytes and in whole Byte increments; sending less than a full Byte will cause the

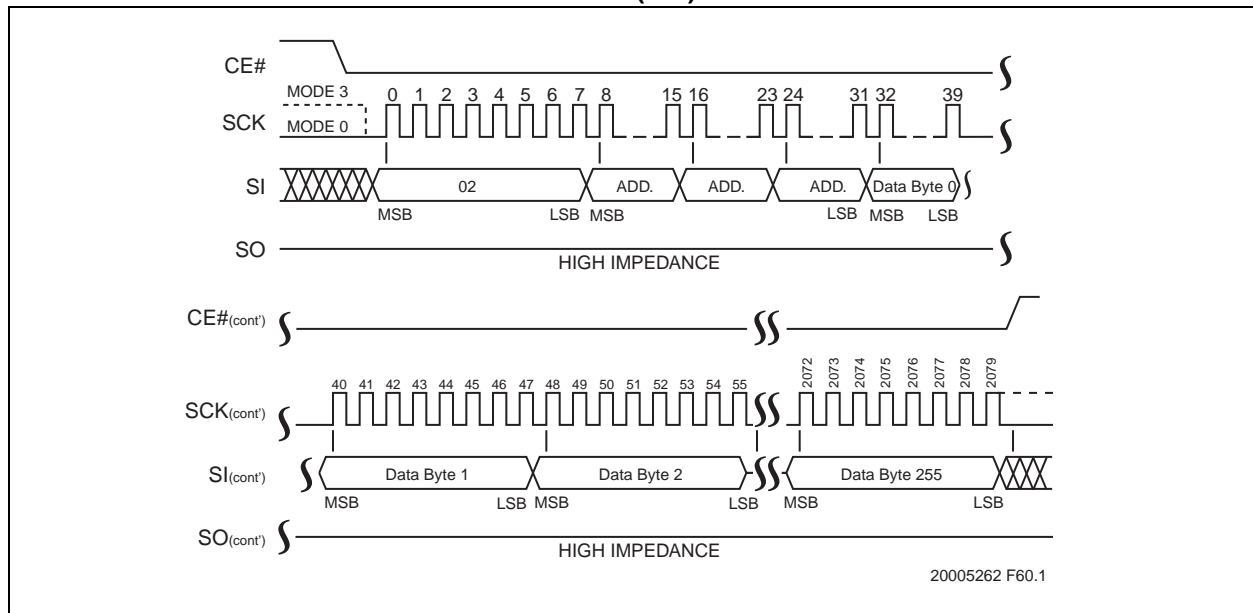
partial Byte to be ignored. Poll the BUSY bit in the Status register, or wait T_{PP} for the completion of the internal, self-timed, Write operation. See Figures 5-25 and 5-26 for the Page-Program sequence.

When executing Page-Program, the memory range for the SST26VF016B is divided into 256 Byte page boundaries. The device handles shifting of more than 256 Bytes of data by maintaining the last 256 Bytes of data as the correct data to be programmed. If the target address for the Page-Program instruction is not the beginning of the page boundary (A[7:0] are not all zero), and the number of bytes of data input exceeds or overlaps the end of the address of the page boundary, the excess data inputs wrap around and will be programmed at the start of that target page.

FIGURE 5-25: PAGE-PROGRAM SEQUENCE (SQI)



FIGURE 5-26: PAGE-PROGRAM SEQUENCE (SPI)



5.21 SPI Quad Page-Program

The SPI Quad Page-Program instruction programs up to 256 Bytes of data in the memory. The data for the selected page address must be in the erased state (FFH) before initiating the SPI Quad Page-Program operation. A SPI Quad Page-Program applied to a protected memory area will be ignored. SST26VF016B requires the ICO bit in the configuration register to be set to '1' prior to executing the command. Prior to the program operation, execute the WREN instruction.

To execute a SPI Quad Page-Program operation, the host drives CE# low then sends the SPI Quad Page-Program command cycle (32H), three address cycles followed by the data to be programmed, then drives CE# high. The programmed data must be between 1 to 256 Bytes and in whole Byte increments. The com-

mand cycle is eight clocks long, the address and data cycles are each two clocks long, most significant bit first. Poll the BUSY bit in the Status register, or wait T_{PP}, for the completion of the internal, self-timed, Write operation. See Figure 5-27.

When executing SPI Quad Page-Program, the memory range for the SST26VF016B is divided into 256 Byte page boundaries. The device handles shifting of more than 256 Bytes of data by maintaining the last 256 Bytes of data as the correct data to be programmed. If the target address for the SPI Quad Page-Program instruction is not the beginning of the page boundary (A[7:0] are not all zero), and the of bytes of data input exceeds or overlaps the end of the address of the page boundary, the excess data inputs wrap around and will be programmed at the start of that target page.

FIGURE 5-27: SPI QUAD PAGE-PROGRAM SEQUENCE



5.22 Write-Suspend and Write-Resume

Write-Suspend allows the interruption of Sector-Erase, Block-Erase, SPI Quad Page-Program, or Page-Program operations in order to erase, program, or read data in another portion of memory. The original operation can be continued with the Write-Resume command. This operation is supported in both SQI and SPI protocols.

Only one write operation can be suspended at a time; if an operation is already suspended, the device will ignore the Write-Suspend command. Write-Suspend during Chip-Erase is ignored; Chip-Erase is not a valid command while a write is suspended. The Write-Resume command is ignored until any write operation (Program or Erase) initiated during the Write-Suspend is complete. The device requires a minimum of 500 μs between each Write-Suspend command.

5.23 Write-Suspend During Sector-Erase or Block-Erase

Issuing a Write-Suspend instruction during Sector-Erase or Block-Erase allows the host to program or read any sector that was not being erased. The device will ignore any programming commands pointing to the suspended sector(s). Any attempt to read from the suspended sector(s) will output unknown data because the Sector- or Block-Erase will be incomplete.

To execute a Write-Suspend operation, the host drives CE# low, sends the Write Suspend command cycle (B0H), then drives CE# high. The Status register indicates that the erase has been suspended by changing the WSE bit from '0' to '1,' but the device will not accept another command until it is ready. To determine when the device will accept a new command, poll the BUSY bit in the Status register or wait T_{WS}.

5.24 Write Suspend During Page Programming or SPI Quad Page Programming

Issuing a Write-Suspend instruction during Page Programming allows the host to erase or read any sector that is not being programmed. Erase commands pointing to the suspended sector(s) will be ignored. Any attempt to read from the suspended page will output unknown data because the program will be incomplete.

To execute a Write Suspend operation, the host drives CE# low, sends the Write Suspend command cycle (B0H), then drives CE# high. The Status register indicates that the programming has been suspended by changing the WSP bit from '0' to '1,' but the device will not accept another command until it is ready. To determine when the device will accept a new command, poll the BUSY bit in the Status register or wait T_{WS} .

5.25 Write-Resume

Write-Resume restarts a Write command that was suspended, and changes the suspend status bit in the Status register (WSE or WSP) back to '0'.

To execute a Write-Resume operation, the host drives CE# low, sends the Write Resume command cycle (30H), then drives CE# high. To determine if the internal, self-timed Write operation completed, poll the BUSY bit in the Status register, or wait the specified time T_{SE} , T_{BE} or T_{PP} for Sector-Erase, Block-Erase, or Page-Programming, respectively. The total write time before suspend and after resume will not exceed the uninterrupted write times T_{SE} , T_{BE} or T_{PP} .

5.26 Read Security ID

The Read Security ID operation is supported in both SPI and SQI modes. To execute a Read Security ID (SID) operation in SPI mode, the host drives CE# low, sends the Read Security ID command cycle (88H), two address cycles, and then one dummy cycle. To execute

a Read Security ID operation in SQI mode, the host drives CE# low and then sends the Read Security ID command, two address cycles, and three dummy cycles.

After the dummy cycles, the device outputs data on the falling edge of the SCK signal, starting from the specified address location. The data output stream is continuous through all SID addresses until terminated by a low-to-high transition on CE#. See [Table 5-5](#) for the Security ID address range.

5.27 Program Security ID

The Program Security ID instruction programs one to 2040 Bytes of data in the user-programmable, Security ID space. This Security ID space is one-time programmable (OTP). The device ignores a Program Security ID instruction pointing to an invalid or protected address, see [Table 5-5](#). Prior to the program operation, execute WREN.

To execute a Program SID operation, the host drives CE# low, sends the Program Security ID command cycle (A5H), two address cycles, the data to be programmed, then drives CE# high. The programmed data must be between 1 to 256 Bytes and in whole Byte increments.

The device handles shifting of more than 256 Bytes of data by maintaining the last 256 Bytes of data as the correct data to be programmed. If the target address for the Program Security ID instruction is not the beginning of the page boundary, and the number of data input exceeds or overlaps the end of the address of the page boundary, the excess data inputs wrap around and will be programmed at the start of that target page.

The Program Security ID operation is supported in both SPI and SQI mode. To determine the completion of the internal, self-timed Program SID operation, poll the BUSY bit in the software status register, or wait T_{PSID} for the completion of the internal self-timed Program Security ID operation.

TABLE 5-5: PROGRAM SECURITY ID

| Program Security ID | Address Range |
|-------------------------------------|---------------|
| Unique ID Pre-Programmed at factory | 0000 – 0007H |
| User Programmable | 0008H – 07FFH |

5.28 Lockout Security ID

The Lockout Security ID instruction prevents any future changes to the Security ID, and is supported in both SPI and SQI modes. Prior to the operation, execute WREN.

To execute a Lockout SID, the host drives CE# low, sends the Lockout Security ID command cycle (85H), then drives CE# high. Poll the BUSY bit in the software status register, or wait T_{PSID}, for the completion of the Lockout Security ID operation.

5.29 Read-Status Register (RDSR) and Read-Configuration Register (RDCR)

The Read-Status Register (RDSR) and Read-Configuration Register (RDCR) commands output the contents of the Status and Configuration registers. These com-

mands function in both SPI and SQI modes. The Status register may be read at any time, even during a Write operation. When a Write is in progress, poll the BUSY bit before sending any new commands to assure that the new commands are properly received by the device.

To Read the Status or Configuration registers, the host drives CE# low, then sends the Read-Status-Register command cycle (05H) or the Read Configuration Register command (35H). A dummy cycle is required in SQI mode. Immediately after the command cycle, the device outputs data on the falling edge of the SCK signal. The data output stream continues until terminated by a low-to-high transition on CE#. See Figures 5-28 and 5-29 for the instruction sequence.

FIGURE 5-28: READ-STATUS-REGISTER AND READ-CONFIGURATION REGISTER SEQUENCE (SQI)



Note: MSN = Most Significant Nibble; LSN = Least Significant Nibble, C[1:0]=05H or 35H

FIGURE 5-29: READ-STATUS-REGISTER AND READ-CONFIGURATION REGISTER SEQUENCE (SPI)



5.30 Write-Status Register (WRSR)

The Write-Status Register (WRSR) command writes new values to the Configuration register. To execute a Write-Status Register operation, the host drives CE#

low, then sends the Write-Status Register command cycle (01H), two cycles of data, and then drives CE# high. Values in the second data cycle will be accepted by the device. See Figures 5-30 and 5-31.

FIGURE 5-30: WRITE-STATUS-REGISTER SEQUENCE (SQI)



FIGURE 5-31: WRITE-STATUS-REGISTER SEQUENCE (SPI)



5.31 Write-Enable (WREN)

The Write Enable (WREN) instruction sets the Write-Enable-Latch bit in the Status register to '1,' allowing Write operations to occur. The WREN instruction must be executed prior to any of the following operations: Sector Erase, Block Erase, Chip Erase, Page Program, Program Security ID, Lockout Security ID, Write Block-

Protection Register, Lock-Down Block-Protection Register, Non-Volatile Write-Lock Lock-Down Register, SPI Quad Page program, and Write-Status Register. To execute a Write Enable the host drives CE# low then sends the Write Enable command cycle (06H) then drives CE# high. See Figures 5-32 and 5-33 for the WREN instruction sequence.

FIGURE 5-32: WRITE-ENABLE SEQUENCE (SQI)



FIGURE 5-33: WRITE-ENABLE SEQUENCE (SPI)



5.32 Write-Disable (WRDI)

The Write-Disable (WRDI) instruction sets the Write-Enable-Latch bit in the Status register to '0,' preventing Write operations. The WRDI instruction is ignored

during any internal write operations. Any Write operation started before executing WRDI will complete. Drive CE# high before executing WRDI.

To execute a Write-Disable, the host drives CE# low, sends the Write Disable command cycle (04H), then drives CE# high. See Figures 5-34 and 5-35.

FIGURE 5-34: WRITE-DISABLE (WRDI) SEQUENCE (SQI)



FIGURE 5-35: WRITE-DISABLE (WRDI) SEQUENCE (SPI)



5.33 Read Block-Protection Register (RBPR)

The Read Block-Protection Register instruction outputs the Block-Protection register data which determines the protection status. To execute a Read Block-Protection Register operation, the host drives CE# low, and then sends the Read Block-Protection Register command cycle (72H). A dummy cycle is required in SQI mode.

After the command cycle, the device outputs data on the falling edge of the SCK signal starting with the most significant bit(s), see Table 5-6 for definitions of each bit in the Block-Protection register. The RBPR command does not wrap around. After all data has been output, the device will output 0H until terminated by a low-to-high transition on CE#.

FIGURE 5-36: READ BLOCK-PROTECTION REGISTER SEQUENCE (SQI)

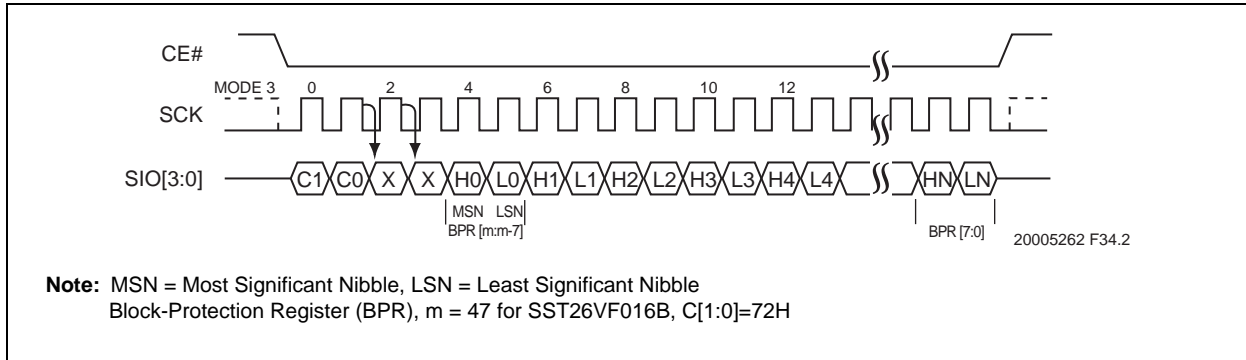


FIGURE 5-37: READ BLOCK-PROTECTION REGISTER SEQUENCE (SPI)



5.34 Write Block-Protection Register (WBPR)

The Write Block-Protection Register (WBPR) command changes the Block-Protection register data to indicate the protection status. Execute WREN before executing WBPR.

To execute a Write Block-Protection Register operation the host drives CE# low, sends the Write Block-Protection Register command cycle (42H), sends 18 cycles of data, and finally drives CE# high. Data input must be most significant bit(s) first. See Table 5-6 for definitions of each bit in the Block-Protection register. See Figures 5-38 and 5-39.

FIGURE 5-38: WRITE BLOCK-PROTECTION REGISTER SEQUENCE (SQI)



FIGURE 5-39: WRITE BLOCK-PROTECTION REGISTER SEQUENCE (SPI)



5.35 Lock-Down Block-Protection Register (LBPR)

The Lock-Down Block-Protection Register instruction prevents changes to the Block-Protection register during device operation. Lock-Down resets after power

cycling; this allows the Block-Protection register to be changed. Execute WREN before initiating the Lock-Down Block-Protection Register instruction.

To execute a Lock-Down Block-Protection Register, the host drives CE# low, then sends the Lock-Down Block-Protection Register command cycle (8DH), then drives CE# high.

FIGURE 5-40: LOCK-DOWN BLOCK-PROTECTION REGISTER (SQI)



FIGURE 5-41: LOCK-DOWN BLOCK-PROTECTION REGISTER (SPI)



5.36 Non-Volatile Write-Lock Lock-Down Register (nVWLDR)

The Non-Volatile Write-Lock Lock-Down Register (nVWLDR) instruction controls the ability to change the Write-Lock bits in the Block-Protection register. Execute WREN before initiating the nVWLDR instruction.

To execute nVWLDR, the host drives CE# low, then sends the nVWLDR command cycle (E8H), followed by 18 cycles of data, and then drives CE# high.

After CE# goes high, the non-volatile bits are programmed and the programming time-out must complete before any additional commands, other than Read Status Register, can be entered. Poll the BUSY bit in the Status register, or wait T_{PP} for the completion of the internal, self-timed, Write operation. Data inputs must be most significant bit(s) first.

FIGURE 5-42: WRITE-LOCK LOCK-DOWN REGISTER SEQUENCE (SQI)

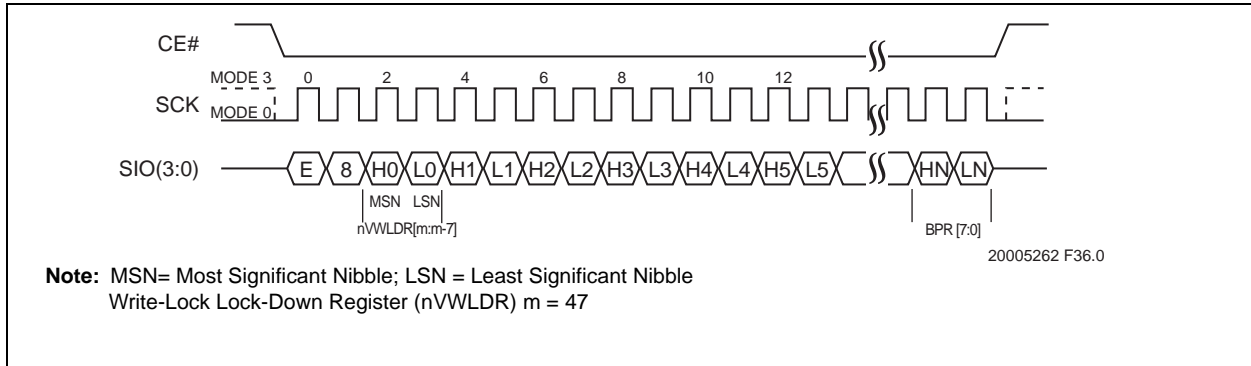
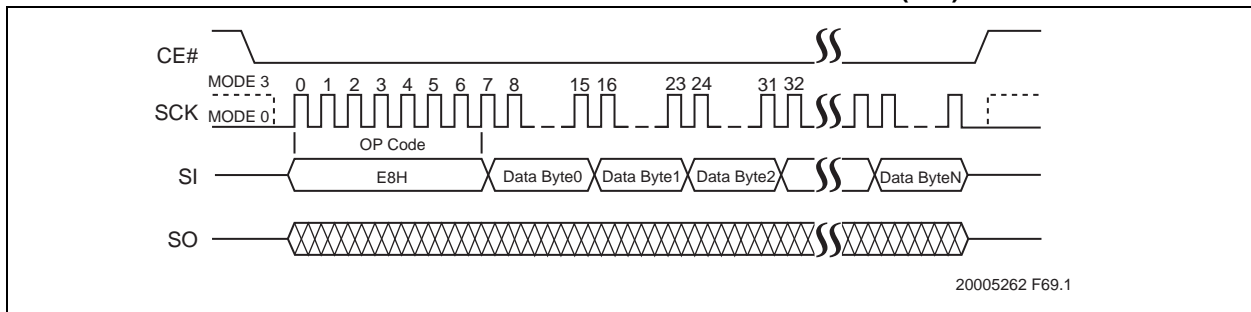


FIGURE 5-43: WRITE-LOCK LOCK-DOWN REGISTER SEQUENCE (SPI)



5.37 Global Block-Protection Unlock (ULBPR)

To execute a ULBPR instruction, the host drives CE# low, then sends the ULBPR command cycle (98H), and then drives CE# high.

The Global Block-Protection Unlock (ULBPR) instruction clears all write-protection bits in the Block-Protection register, except for those bits that have been locked down with the nVWLDLDR command. Execute WREN before initiating the ULBPR instruction.

FIGURE 5-44: GLOBAL BLOCK-PROTECTION UNLOCK (SQI)

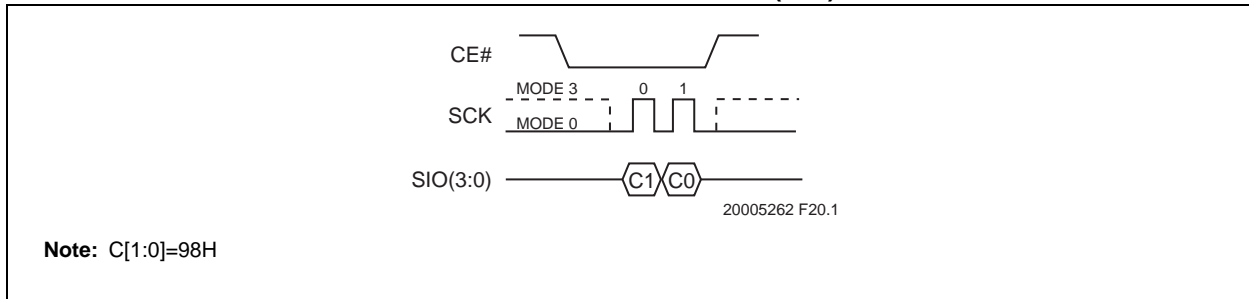


FIGURE 5-45: GLOBAL BLOCK-PROTECTION UNLOCK (SPI)

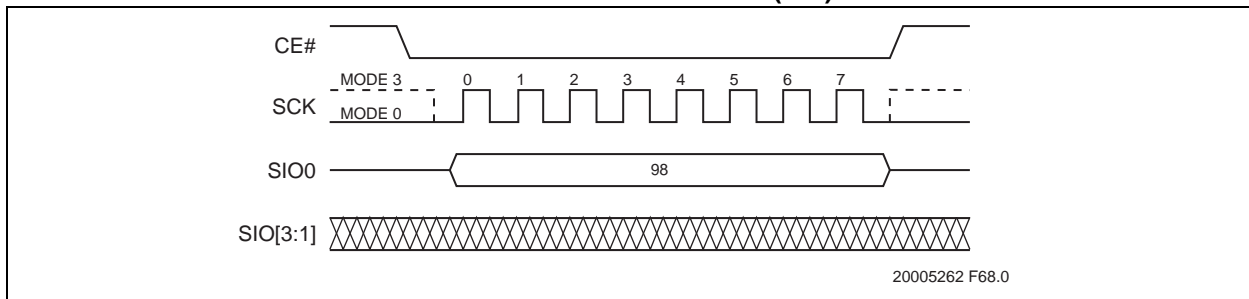


TABLE 5-6: BLOCK-PROTECTION REGISTER FOR SST26VF016B ¹

| BPR Bits | | Address Range | Protected Block Size |
|-----------|----------------------------------|--------------------|----------------------|
| Read Lock | Write Lock/nVWLDLDR ² | | |
| 47 | 46 | 1FE000H - 1FFFFFFH | 8 KByte |
| 45 | 44 | 1FC000H - 1FDFFFH | 8 KByte |
| 43 | 42 | 1FA000H - 1FBFFFH | 8 KByte |
| 41 | 40 | 1F8000H - 1F9FFFH | 8 KByte |
| 39 | 38 | 006000H - 007FFFH | 8 KByte |
| 37 | 36 | 004000H - 005FFFH | 8 KByte |
| 35 | 34 | 002000H - 003FFFH | 8 KByte |
| 33 | 32 | 000000H - 001FFFH | 8 KByte |
| | 31 | 1F0000H - 1F7FFFH | 32 KByte |
| | 30 | 008000H - 00FFFFH | 32 KByte |
| | 29 | 1E0000H - 1EFFFFH | 64 KByte |
| | 28 | 1D0000H - 1DFFFFH | 64 KByte |
| | 27 | 1C0000H - 1CFFFFH | 64 KByte |
| | 26 | 1B0000H - 1BFFFFH | 64 KByte |
| | 25 | 1A0000H - 1AFFFFH | 64 KByte |
| | 24 | 190000H - 19FFFFH | 64 KByte |
| | 23 | 180000H - 18FFFFH | 64 KByte |
| | 22 | 170000H - 17FFFFH | 64 KByte |
| | 21 | 160000H - 16FFFFH | 64 KByte |
| | 20 | 150000H - 15FFFFH | 64 KByte |
| | 19 | 140000H - 14FFFFH | 64 KByte |
| | 18 | 130000H - 13FFFFH | 64 KByte |
| | 17 | 120000H - 12FFFFH | 64 KByte |
| | 16 | 110000H - 11FFFFH | 64 KByte |
| | 15 | 100000H - 10FFFFH | 64 KByte |
| | 14 | 0F0000H - 0FFFFFFH | 64 KByte |
| | 13 | 0E0000H - 0EFFFFH | 64 KByte |
| | 12 | 0D0000H - 0DFFFFH | 64 KByte |
| | 11 | 0C0000H - 0CFFFFH | 64 KByte |
| | 10 | 0B0000H - 0BFFFFH | 64 KByte |
| | 9 | 0A0000H - 0AFFFFH | 64 KByte |
| | 8 | 090000H - 09FFFFH | 64 KByte |
| | 7 | 080000H - 08FFFFH | 64 KByte |
| | 6 | 070000H - 07FFFFH | 64 KByte |
| | 5 | 060000H - 06FFFFH | 64 KByte |
| | 4 | 050000H - 05FFFFH | 64 KByte |
| | 3 | 040000H - 04FFFFH | 64 KByte |
| | 2 | 030000H - 03FFFFH | 64 KByte |
| | 1 | 020000H - 02FFFFH | 64 KByte |
| | 0 | 010000H - 01FFFFH | 64 KByte |

1. The default state after a power-on reset is write-protected BPR[47:0] = 5555 FFFF FFFF
 2. nVWLDLDR bits are one-time-programmable. Once a WLLDR bit is set, the protection state of that particular block is permanently write-locked.

5.38 Deep Power-Down

The Deep Power-down (DPD) instruction puts the device in the lowest power consumption mode—the Deep Power-down mode. The Deep Power-down instruction is ignored during an internal write operation. While the device is in Deep Power-down mode, all instructions will be ignored except for the Release Deep Power-down instruction.

Enter Deep Power-down mode by initiating the Deep Power-down (DPD) instruction (B9H) while driving CE# low. CE# must be driven high before executing the DPD instruction. After CE# is driven high, it requires a delay of T_{DPD} before the standby current I_{SB} is reduced to deep power-down current I_{DPD} . See Table 5-7 for Deep Power-down timing. If the device is busy performing an internal erase or program operation, initiating a Deep Power-down instruction will not place the device in Deep Power-down mode. See Figures 5-46 and 5-47 for the DPD instruction sequence.

TABLE 5-7: DEEP POWER-DOWN

| Symbol | Parameter | Min | Max | Units |
|--------|-----------------------------|-----|-----|---------|
| TDPD | CE# High to Deep Power-down | | 3 | μ s |
| TSBR | CE# High to Standby Mode | | 10 | μ s |

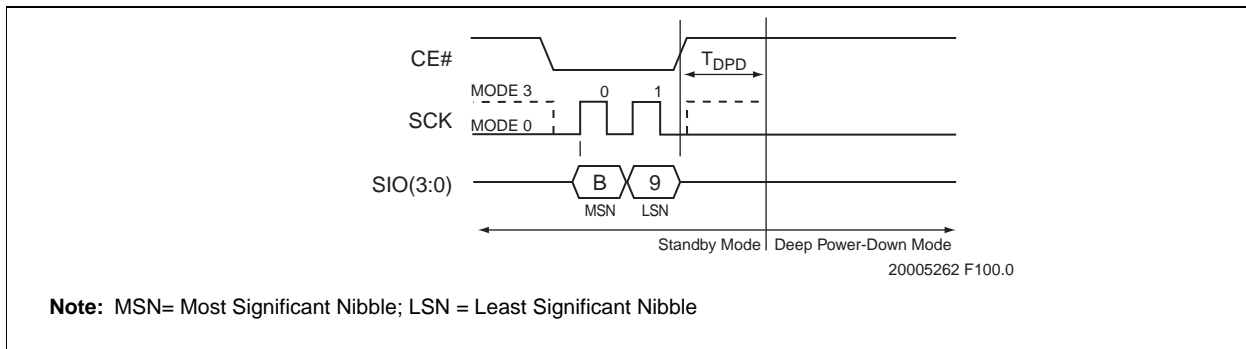


FIGURE 5-46: DEEP POWER-DOWN (DPD) SEQUENCE—SQI MODE

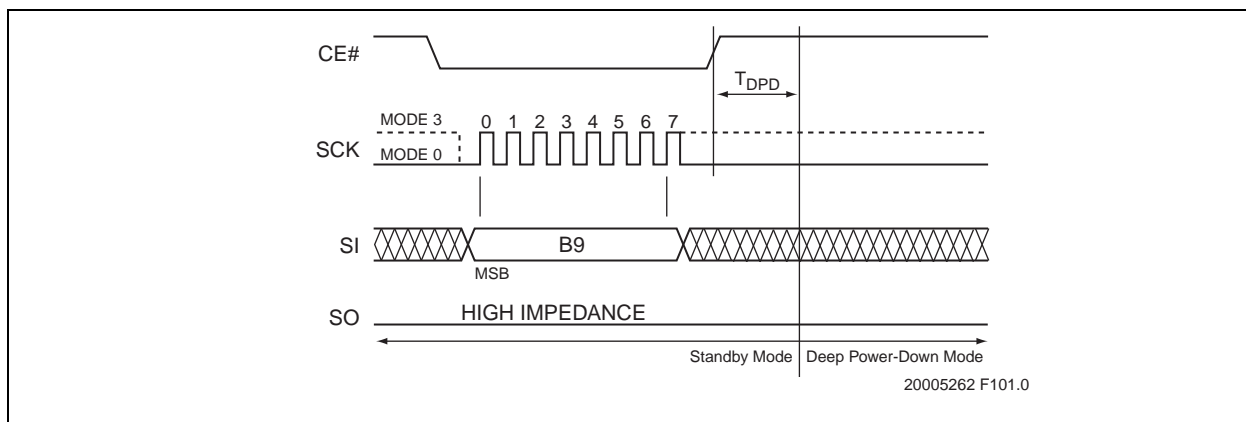


FIGURE 5-47: DEEP POWER-DOWN (DPD)—SPI MODE

5.39 Release from Deep Power-Down and Read ID

Release from Deep Power-Down (RDPD) and Read ID instruction exits Deep Power-down mode. To exit Deep Power down mode, execute the RDPD. During this command, the host drives CE# low, then sends the Deep Power-Down command cycle (ABH), and then drives CE# high. The device will return to Standby mode and be ready for the next instruction after T_{SBR} .

To execute RDPD and read the Device ID, the host drives CE# low then sends the Deep Power-Down command cycle (ABH), three dummy clock cycles, and then drives CE# high. The device outputs the Device ID on the falling edge of the SCK signal following the dummy cycles. The data output stream is continuous until terminated by a low-to-high transition on CE, and will return to Standby mode and be ready for the next instruction after T_{SBR} . See Figures 5-48 and 5-49 for the command sequence.

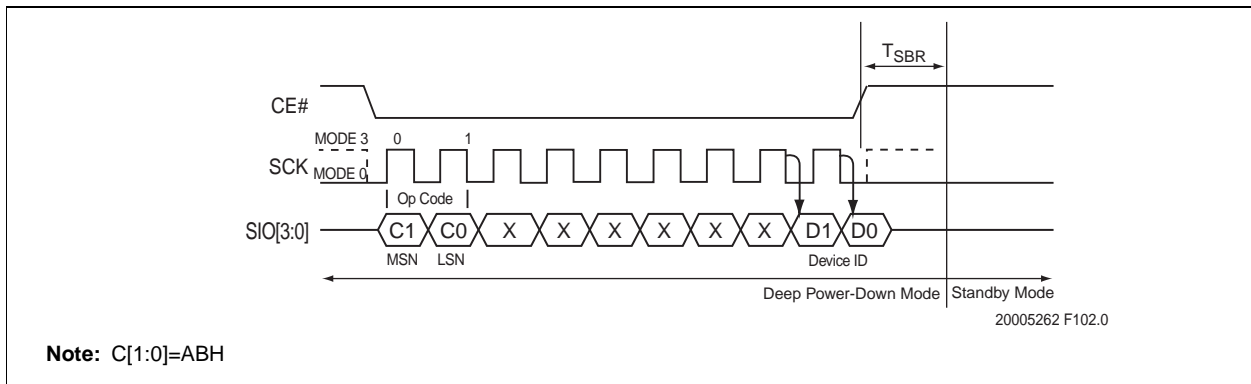


FIGURE 5-48: RELEASE FROM DEEP POWER-DOWN (RDPD) AND READ ID SEQUENCE—SSI MODE

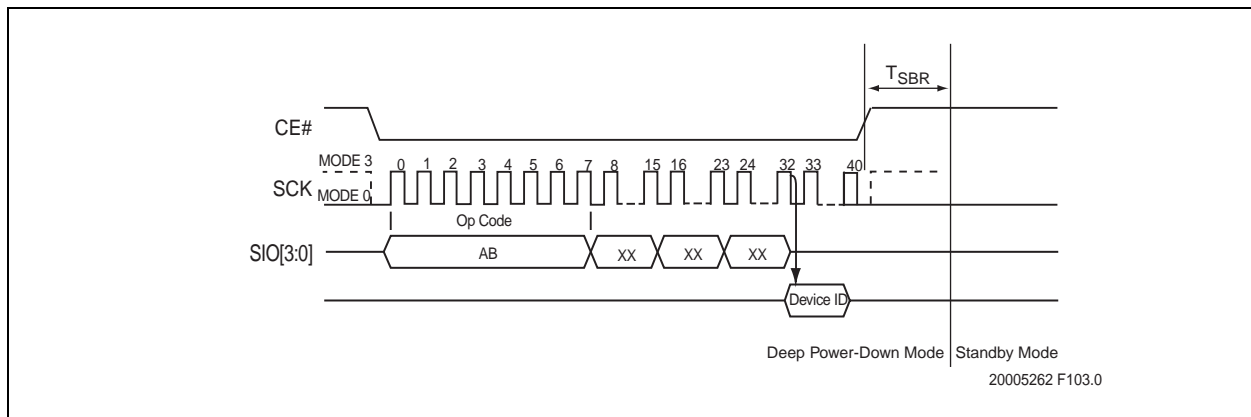


FIGURE 5-49: RELEASE FROM DEEP POWER-DOWN (RDPD) AND READ ID SEQUENCE—SPI MODE

6.0 ELECTRICAL SPECIFICATIONS

Absolute Maximum Stress Ratings (Applied conditions greater than those listed under “Absolute Maximum Stress Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

| | |
|---|------------------------|
| Temperature Under Bias | -55°C to +125°C |
| Storage Temperature | -65°C to +150°C |
| D. C. Voltage on Any Pin to Ground Potential. | -0.5V to $V_{DD}+0.5V$ |
| Transient Voltage (<20 ns) on Any Pin to Ground Potential | -2.0V to $V_{DD}+2.0V$ |
| Package Power Dissipation Capability ($T_A = 25^\circ C$) | 1.0W |
| Surface Mount Solder Reflow Temperature | 260°C for 10 seconds |
| Output Short Circuit Current ¹ | 50 mA |

1. Output shorted for no more than one second. No more than one output shorted at a time.

TABLE 6-1: OPERATING RANGE

| Range | Ambient Temp | V_{DD} |
|------------|-----------------|----------|
| Industrial | -40°C to +85°C | 2.7-3.6V |
| Extended | -40°C to +105°C | |

TABLE 6-2: AC CONDITIONS OF TEST¹

| Input Rise/Fall Time | Output Load |
|----------------------|---------------|
| 3ns | $C_L = 30$ pF |

1. See [Figure 8-5](#)

6.1 Power-Up Specifications

All functionalities and DC specifications are specified for a V_{DD} ramp rate of greater than 1V per 100 ms (0V to 3.0V in less than 300 ms). See [Table 6-3](#) and [Figure 6-1](#) for more information.

When V_{DD} drops from the operating voltage to below the minimum V_{DD} threshold at power-down, all operations are disabled and the device does not respond to commands. Data corruption may result if a power-down occurs while a Write-Registers, program, or erase operation is in progress. See [Figure 6-2](#).

TABLE 6-3: RECOMMENDED SYSTEM POWER-UP/DOWN TIMINGS

| Symbol | Parameter | Minimum | Max | Units | Condition |
|------------------|---------------------------------|---------|-----|---------|----------------|
| $T_{PU-READ}^1$ | V_{DD} Min to Read Operation | 100 | | μs | |
| $T_{PU-WRITE}^1$ | V_{DD} Min to Write Operation | 100 | | μs | |
| T_{PD}^1 | Power-down Duration | 100 | | ms | |
| V_{OFF} | V_{DD} off time | | 0.3 | V | 0V recommended |

1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

FIGURE 6-1: POWER-UP TIMING DIAGRAM

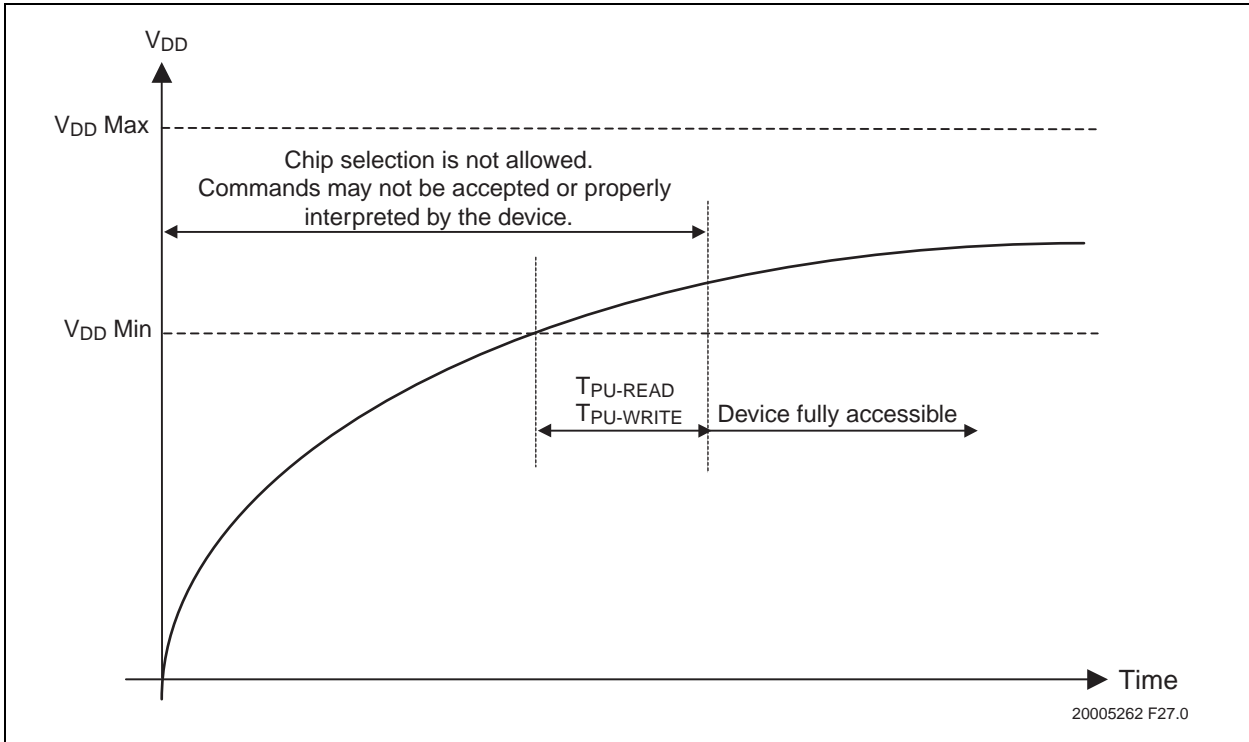
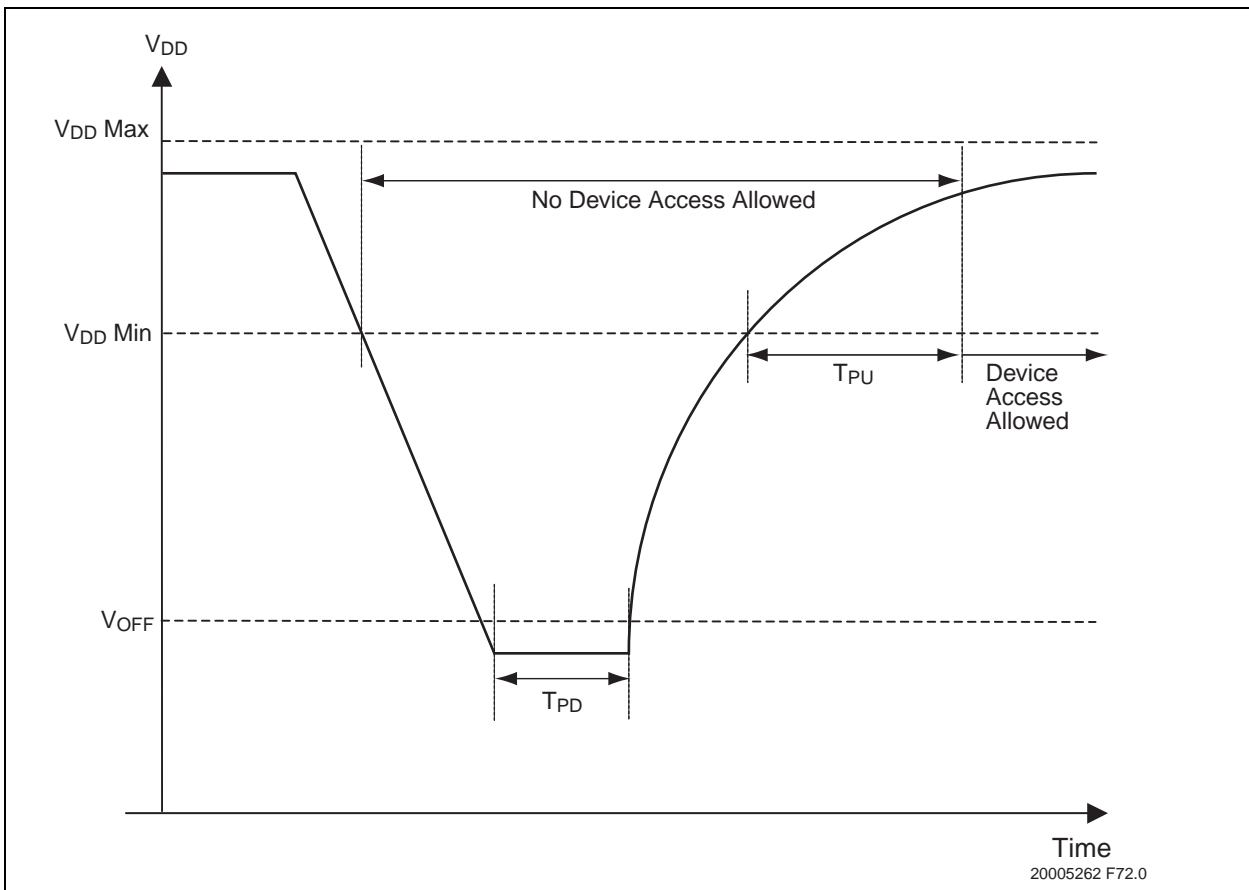


FIGURE 6-2: POWER-DOWN AND VOLTAGE DROP DIAGRAM



7.0 DC CHARACTERISTICS

TABLE 7-1: DC OPERATING CHARACTERISTICS (V_{DD} = 2.3-3.6V)

| Symbol | Parameter | Limits | | | | Test Conditions |
|-------------------|---------------------------|----------------------|-----|-----|-------|---|
| | | Min | Typ | Max | Units | |
| I _{DDR1} | Read Current | | 8 | 15 | mA | V _{DD} =V _{DD} Max, CE#=0.1 V _{DD} /0.9 V _{DD} @40 MHz, SO=open |
| I _{DDR2} | Read Current | | | 20 | mA | V _{DD} = V _{DD} Max, CE#=0.1 V _{DD} /0.9 V _{DD} @104 MHz, SO=open |
| I _{DDW} | Program and Erase Current | | | 25 | mA | V _{DD} Max |
| I _{SB} | Standby Current | | 15 | 45 | μA | CE#=V _{DD} , V _{IN} =V _{DD} or V _{SS} |
| I _{DPD} | Deep Power-down Current | | 8 | 25 | μA | CE#=V _{DD} , V _{IN} =V _{DD} or V _{SS} |
| I _{LI} | Input Leakage Current | | | 2 | μA | V _{IN} =GND to V _{DD} , V _{DD} =V _{DD} Max |
| I _{LO} | Output Leakage Current | | | 2 | μA | V _{OUT} =GND to V _{DD} , V _{DD} =V _{DD} Max |
| V _{IL} | Input Low Voltage | | | 0.8 | V | V _{DD} =V _{DD} Min |
| V _{IH} | Input High Voltage | 0.7 V _{DD} | | | V | V _{DD} =V _{DD} Max |
| V _{OL} | Output Low Voltage | | | 0.2 | V | I _{OL} =100 μA, V _{DD} =V _{DD} Min |
| V _{OH} | Output High Voltage | V _{DD} -0.2 | | | V | I _{OH} =-100 μA, V _{DD} =V _{DD} Min |

TABLE 7-2: CAPACITANCE (TA = 25°C, F=1 MHZ, OTHER PINS OPEN)

| Parameter | Description | Test Condition | Maximum |
|-------------------------------|------------------------|-----------------------|---------|
| C _{OUT} ¹ | Output Pin Capacitance | V _{OUT} = 0V | 8 pF |
| C _{IN} ¹ | Input Capacitance | V _{IN} = 0V | 6 pF |

1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 7-3: RELIABILITY CHARACTERISTICS

| Symbol | Parameter | Minimum Specification | Units | Test Method |
|-------------------------------|----------------|-----------------------|--------|---------------------|
| N _{END} ¹ | Endurance | 100,000 | Cycles | JEDEC Standard A117 |
| T _{DR} ¹ | Data Retention | 100 | Years | JEDEC Standard A103 |
| I _{LTH} ¹ | Latch Up | 100 + I _{DD} | mA | JEDEC Standard 78 |

1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 7-4: WRITE TIMING PARAMETERS (V_{DD} = 2.3-3.6V)

| Symbol | Parameter | Minimum | Maximum | Units |
|------------------------------|-------------------------------------|---------|---------|-------|
| T _{SE} | Sector-Erase | | 25 | ms |
| T _{BE} | Block-Erase | | 25 | ms |
| T _{SCE} | Chip-Erase | | 50 | ms |
| T _{PP} ¹ | Page-Program | | 1.5 | ms |
| T _{PSID} | Program Security-ID | | 1.5 | ms |
| T _{WS} | Write-Suspend Latency | | 25 | μs |
| T _{Wpen} | Write-Protection Enable Bit Latency | | 25 | ms |

1. Estimate for typical conditions less than 256 bytes: Programming Time (μs) = 55 + (3.75 x # of bytes)

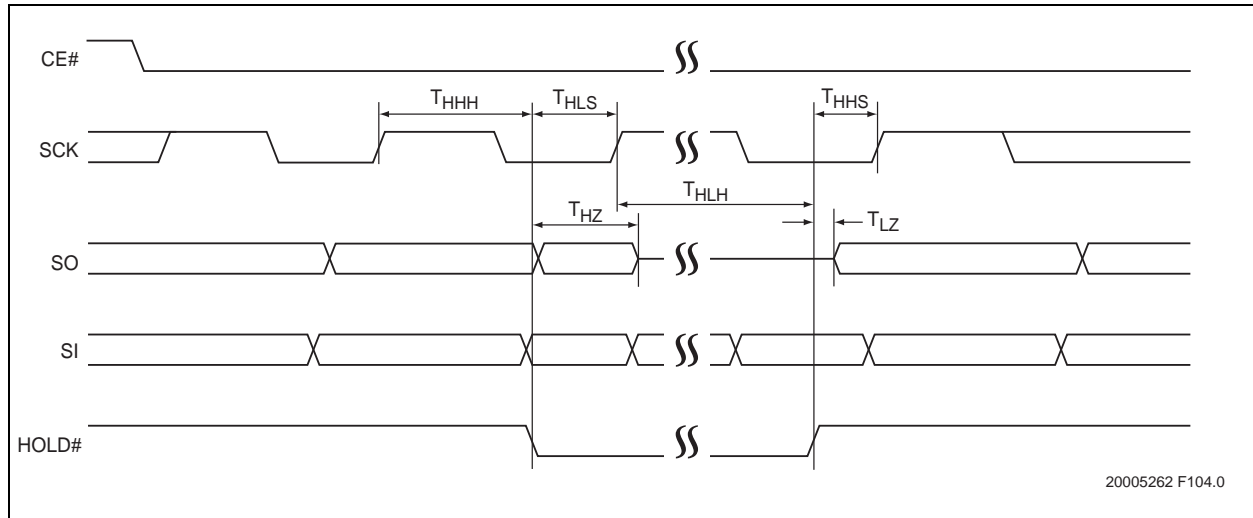
8.0 AC CHARACTERISTICS

TABLE 8-1: AC OPERATING CHARACTERISTICS ($V_{DD}^1 = 2.3-3.6V$)

| Symbol | Parameter | Limits - 40 MHz | | Limits - 80 MHz | | Limits - 104 MHz | | Units |
|--------------|------------------------------------|-----------------|---------|-----------------|---------|------------------|---------|-------|
| | | Min | Max | Min | Max | Min | Max | |
| F_{CLK} | Serial Clock Frequency | | 40 | | 80 | | 104 | MHz |
| T_{CLK} | Serial Clock Period | | 25 | | 12.5 | | 9.6 | ns |
| T_{SCKH} | Serial Clock High Time | 11 | | 5.5 | | 4.5 | | ns |
| T_{SCKL} | Serial Clock Low Time | 11 | | 5.5 | | 4.5 | | ns |
| T_{SCKR}^2 | Serial Clock Rise Time (slew rate) | 0.1 | | 0.1 | | 0.1 | | V/ns |
| T_{SCKF}^2 | Serial Clock Fall Time (slew rate) | 0.1 | | 0.1 | | 0.1 | | V/ns |
| T_{CES}^3 | CE# Active Setup Time | 8 | | 5 | | 5 | | ns |
| T_{CEH}^3 | CE# Active Hold Time | 8 | | 5 | | 5 | | ns |
| T_{CHS}^3 | CE# Not Active Setup Time | 8 | | 5 | | 5 | | ns |
| T_{CHH}^3 | CE# Not Active Hold Time | 8 | | 5 | | 5 | | ns |
| T_{CPH} | CE# High Time | 25 | | 12.5 | | 12 | | ns |
| T_{CHZ} | CE# High to High-Z Output | | 19 | | 12.5 | | 12 | ns |
| T_{CLZ} | SCK Low to Low-Z Output | 0 | | 0 | | 0 | | ns |
| T_{HLS} | HOLD# Low Setup Time | 8 | | 5 | | 5 | | ns |
| T_{HHS} | HOLD# High Setup Time | 8 | | 5 | | 5 | | ns |
| T_{HLH} | HOLD# Low Hold Time | 8 | | 5 | | 5 | | ns |
| T_{HHH} | HOLD# High Hold Time | 8 | | 5 | | 5 | | ns |
| T_{HZ} | HOLD# Low-to-High-Z Output | | 8 | | 8 | | 8 | ns |
| T_{LZ} | HOLD# High-to-Low-Z Output | | 8 | | 8 | | 8 | ns |
| T_{DS} | Data In Setup Time | 3 | | 3 | | 3 | | ns |
| T_{DH} | Data In Hold Time | 4 | | 4 | | 4 | | ns |
| T_{OH} | Output Hold from SCK Change | 0 | | 0 | | 0 | | ns |
| T_V | Output Valid from SCK | | $8/5^4$ | | $8/5^4$ | | $8/5^4$ | ns |

1. Maximum operating frequency for 2.7-3.6V is 104 MHz and for 2.3-3.6V is 80 MHz.
2. Maximum Rise and Fall time may be limited by T_{SCKH} and T_{SCKL} requirements
3. Relative to SCK.
4. 30 pF/10 pF

FIGURE 8-1: HOLD TIMING DIAGRAM



20005262 F104.0

FIGURE 8-2: SERIAL INPUT TIMING DIAGRAM

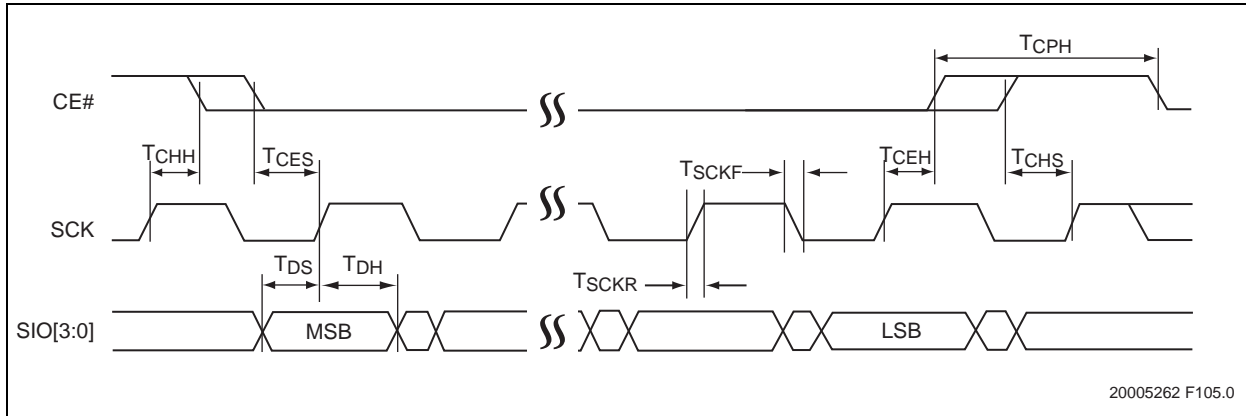


FIGURE 8-3: SERIAL OUTPUT TIMING DIAGRAM

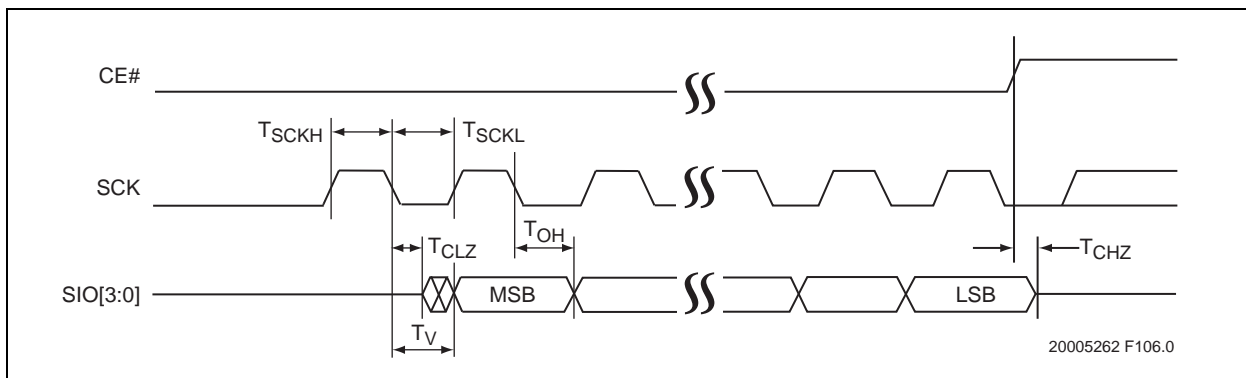
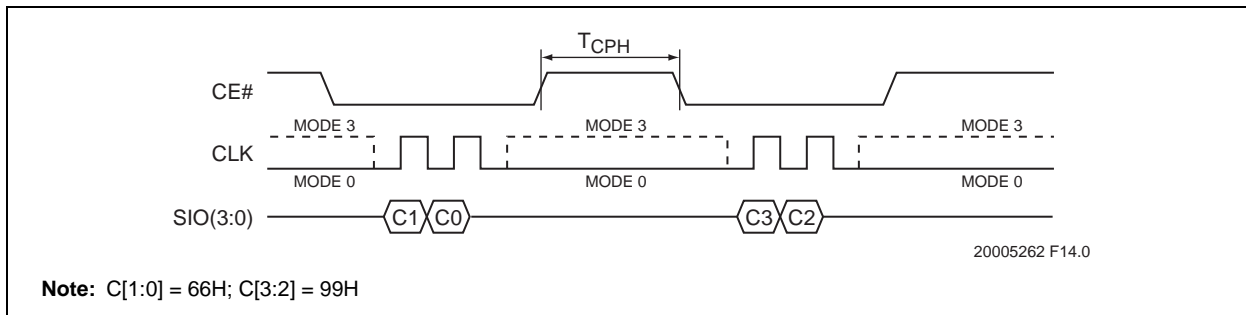


TABLE 8-2: RESET TIMING PARAMETERS

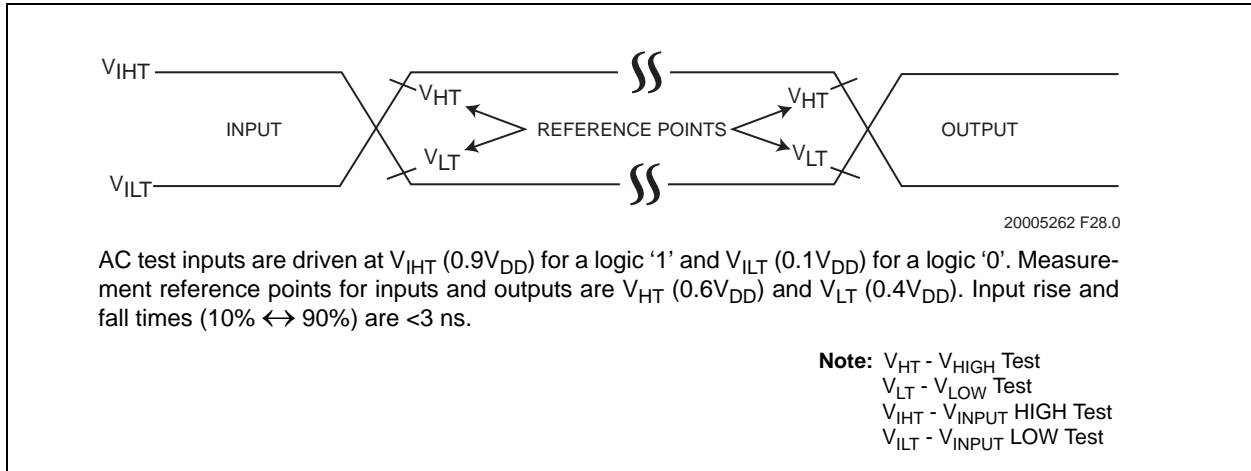
| T _{R(i)} | Parameter | Minimum | Maximum | Units |
|-------------------|--|---------|---------|-------|
| T _{R(o)} | Reset to Read (non-data operation) | | 20 | ns |
| T _{R(p)} | Reset Recovery from Program or Suspend | | 100 | μs |
| T _{R(e)} | Reset Recovery from Erase | | 1 | ms |

FIGURE 8-4: RESET TIMING DIAGRAM



Note: C[1:0] = 66H; C[3:2] = 99H

FIGURE 8-5: AC INPUT/OUTPUT REFERENCE WAVEFORMS



9.0 PACKAGING INFORMATION

9.1 Package Marking

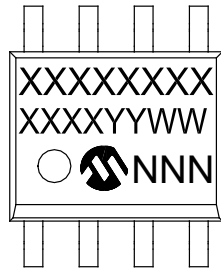
8-Lead SOIJ (5.28 mm)



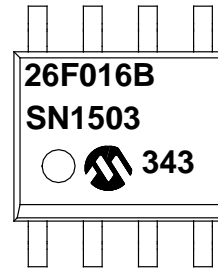
Example



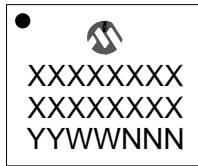
8-Lead SOIC (3.90 mm)



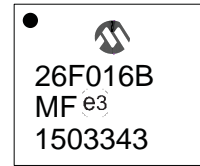
Example



8-Lead WDFN (5x6 mm)



Example



| Part Number | 1st Line Marking Codes | | |
|-------------|------------------------|---------|---------|
| | SOIJ | SOIC | WDFN |
| SST26VF016B | 26F016B | 26F016B | 26F016B |

| | | |
|----------------|--------|--|
| Legend: | XX...X | Part number or part number code |
| | Y | Year code (last digit of calendar year) |
| | YY | Year code (last 2 digits of calendar year) |
| | WW | Week code (week of January 1 is week '01') |
| | NNN | Alphanumeric traceability code (2 characters for small packages) |
| | (e3) | Pb-free JEDEC® designator for Matte Tin (Sn) |

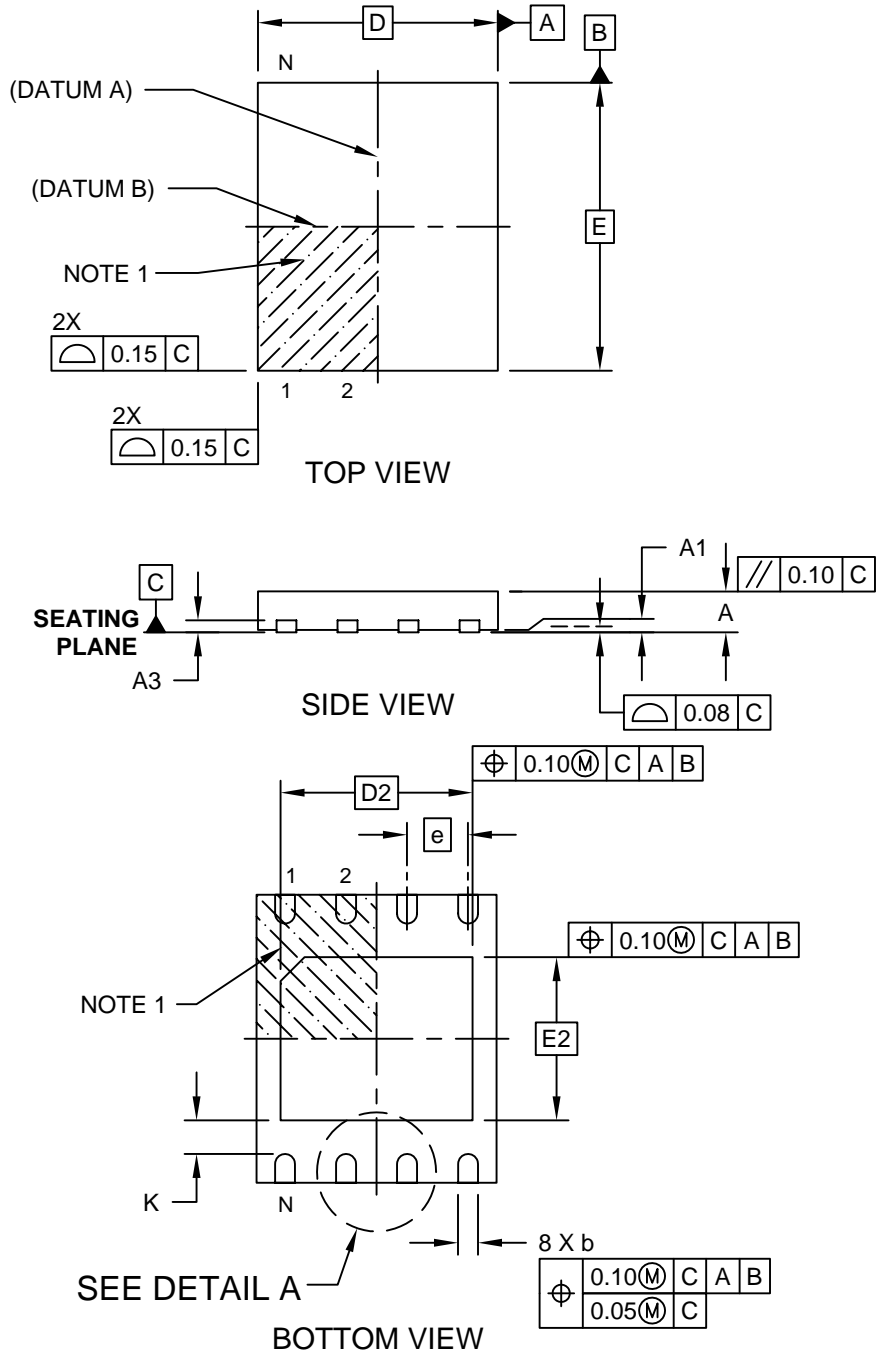
Note: For very small packages with no room for the Pb-free JEDEC® designator (e3), the marking will only appear on the outer carton or reel label.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

9.2 Packaging Diagrams

8-Lead Plastic Very, Very Thin Small Outline No-Lead (MF) - 5x6 mm Body [WDFN]

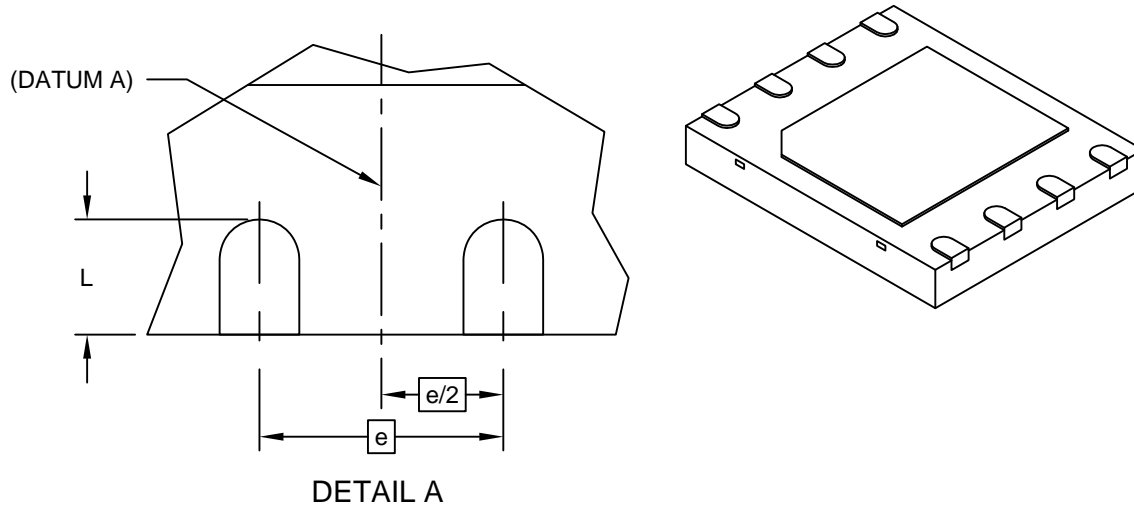
Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Microchip Technology Drawing C04-210B Sheet 1 of 2

8-Lead Plastic Very, Very Thin Small Outline No-Lead (MF) - 5x6 mm Body [WDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



| Dimension Limits | Units | MILLIMETERS | | |
|-------------------------|-------|-------------|------|------|
| | | MIN | NOM | MAX |
| Number of Terminals | N | 8 | | |
| Pitch | e | 1.27 BSC | | |
| Overall Height | A | 0.70 | 0.75 | 0.80 |
| Standoff | A1 | 0.00 | 0.02 | 0.05 |
| Terminal Thickness | A3 | 0.20 REF | | |
| Overall Width | D | 5.00 BSC | | |
| Exposed Pad Width | D2 | 4.00 BSC | | |
| Overall Length | E | 6.00 BSC | | |
| Exposed Pad Length | E2 | 3.40 BSC | | |
| Terminal Width | b | 0.35 | 0.42 | 0.48 |
| Terminal Length | L | 0.50 | 0.60 | 0.70 |
| Terminal-to-Exposed-Pad | K | 0.20 | - | - |

Notes:

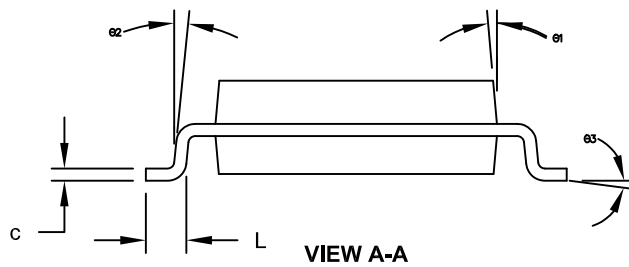
- Pin 1 visual index feature may vary, but must be located within the hatched area.
- Package is saw singulated
- Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

8-Lead Plastic Small Outline (SM) - Medium, 5.28 mm Body [SOIJ]

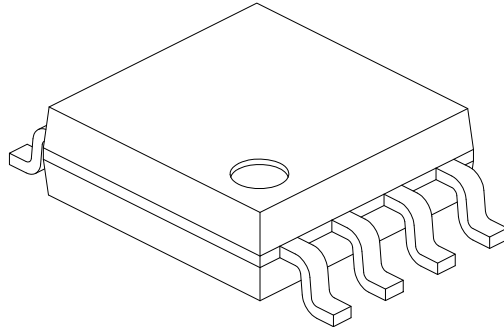
Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Microchip Technology Drawing C04-056C Sheet 1 of 2

8-Lead Plastic Small Outline (SM) - Medium, 5.28 mm Body [SOIJ]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



| Dimension Limits | Units | MILLIMETERS | | |
|--------------------------|-------|-------------|-----|------|
| | | MIN | NOM | MAX |
| Number of Pins | N | 8 | | |
| Pitch | e | 1.27 BSC | | |
| Overall Height | A | 1.77 | - | 2.03 |
| Standoff § | A1 | 0.05 | | 0.25 |
| Molded Package Thickness | A2 | 1.75 | - | 1.98 |
| Overall Width | E | 7.94 BSC | | |
| Molded Package Width | E1 | 5.25 BSC | | |
| Overall Length | D | 5.26 BSC | | |
| Foot Length | L | 0.51 | - | 0.76 |
| Lead Thickness | c | 0.15 | - | 0.25 |
| Lead Width | b | 0.36 | - | 0.51 |
| Mold Draft Angle | Ø1 | - | - | 15° |
| Lead Angle | Ø2 | 0° | - | 8° |
| Foot Angle | Ø3 | 0° | - | 8° |

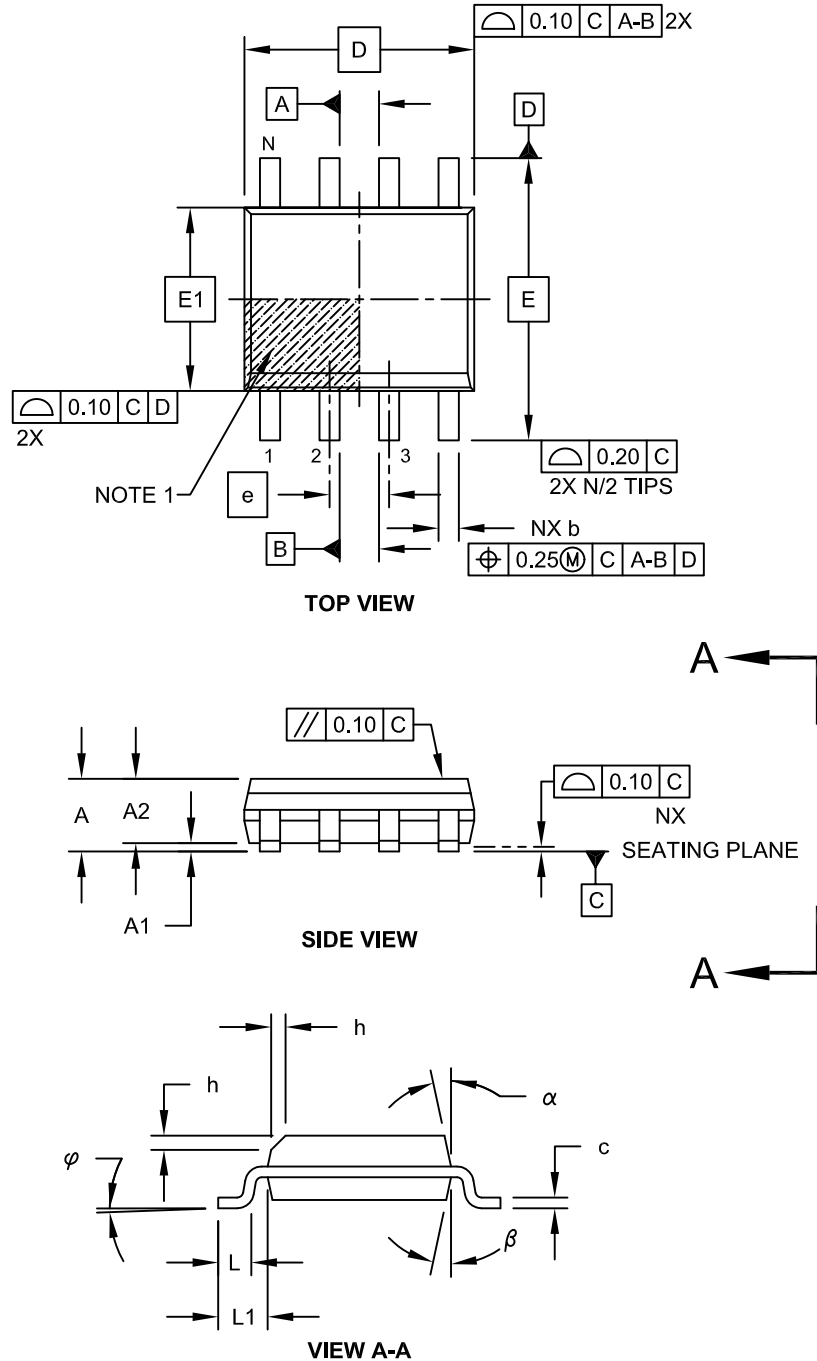
Notes:

1. SOIJ, JEITA/EIAJ Standard, Formerly called SOIC
2. § Significant Characteristic
3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.25mm per side.

Microchip Technology Drawing No. C04-056C Sheet 2 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Microchip Technology Drawing No. C04-057C Sheet 1 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



| Dimension Limits | Units | MILLIMETERS | | |
|--------------------------|-----------|-------------|-----|------|
| | | MIN | NOM | MAX |
| Number of Pins | N | 8 | | |
| Pitch | e | 1.27 BSC | | |
| Overall Height | A | - | - | 1.75 |
| Molded Package Thickness | A2 | 1.25 | - | - |
| Standoff § | A1 | 0.10 | - | 0.25 |
| Overall Width | E | 6.00 BSC | | |
| Molded Package Width | E1 | 3.90 BSC | | |
| Overall Length | D | 4.90 BSC | | |
| Chamfer (Optional) | h | 0.25 | - | 0.50 |
| Foot Length | L | 0.40 | - | 1.27 |
| Footprint | L1 | 1.04 REF | | |
| Foot Angle | φ | 0° | - | 8° |
| Lead Thickness | c | 0.17 | - | 0.25 |
| Lead Width | b | 0.31 | - | 0.51 |
| Mold Draft Angle Top | α | 5° | - | 15° |
| Mold Draft Angle Bottom | β | 5° | - | 15° |

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. § Significant Characteristic
3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

TABLE 9-1: REVISION HISTORY

| Revision | Description | Date |
|-----------------|---|-------------|
| A | <ul style="list-style-type: none">Initial release of data sheet | May 2014 |
| B | <ul style="list-style-type: none">Removed the SST26VF016BA device from the data sheetAdded Part Markings | Feb 2015 |
| C | <ul style="list-style-type: none">Extended the voltage rangeAdded Extended temperature range. | Aug 2015 |

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- **General Technical Support** – Frequently Asked Questions (FAQ), technical support requests, online discussion groups, Microchip consultant program member listing
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10.0 PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

| PART NO. | | X | - | XXX | X | / | XX |
|----------------------|----------------------------|----------|----------|---|--------------------|----------|----------------|
| Device | Tape/Reel Indicator | | | Operating Frequency | Temperature | | Package |
| Device: | SST26VF016B | | | = 16 Mbit, 2.5V/3.0V, SQI Flash Memory WP#/Hold# pin Enable at power-up | | | |
| Tape and Reel Flag: | T (blank) | | | = Tape and Reel = Tube or Tray | | | |
| Operating Frequency: | 104 | | | = 104 MHz | | | |
| Temperature: | I V | | | = -40°C to +85°C = -40°C to +105°C | | | |
| Package: | MF SM SN | | | = WDFN (6mm x 5mm Body), 8-lead = SOIJ (5.28 mm Body), 8-lead = SOIC (3.90 mm Body), 8-lead | | | |

Valid Combinations:

- SST26VF016B-104I/SM
- SST26VF016BT-104I/SM
- SST26VF016B-104I/SN
- SST26VF016BT-104I/SN
- SST26VF016B-104I/MF
- SST26VF016BT-104I/MF
- SST26VF016B-104V/SM
- SST26VF016BT-104V/SM
- SST26VF016B-104V/SN
- SST26VF016BT-104V/SN
- SST26VF016B-104V/MF
- SST26VF016BT-104V/MF

11.0 APPENDIX

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (1 OF 16)

| Address | Bit Address | Data | Comments |
|--|-------------|------|---|
| SFDP Header | | | |
| SFDP Header: 1st DWORD | | | |
| 00H | A7:A0 | 53H | SFDP Signature SFDP Signature=50444653H |
| 01H | A15:A8 | 46H | |
| 02H | A23:A16 | 44H | |
| 03H | A31:A24 | 50H | |
| SFDP Header: 2nd DWORD | | | |
| 04H | A7:A0 | 06H | SFDP Minor Revision Number |
| 05H | A15:A8 | 01H | SFDP Major Revision Number |
| 06H | A23:A16 | 02H | Number of Parameter Headers (NPH)=3 |
| 07H | A31:A24 | FFH | Unused. Contains FF and can not be changed. |
| Parameter Headers | | | |
| JEDEC Flash Parameter Header: 1st DWORD | | | |
| 08H | A7:A0 | 00H | Parameter ID Least Significant Bit (LSB) Number. When this field is set to 00H, it indicates a JEDEC-specified header. For vendor-specified headers, this field must be set to the vendor's manufacturer ID. |
| 09H | A15:A8 | 06H | Parameter Table Minor Revision Number Minor revisions are either clarifications or changes that add parameters in existing Reserved locations. Minor revisions do NOT change overall structure of SFDP. Minor Revision starts at 00H. |
| 0AH | A23:A16 | 01H | Parameter Table Major Revision Number Major revisions are changes that reorganize or add parameters to locations that are NOT currently Reserved. Major revisions would require code (BIOS/firmware) or hardware change to get previously defined discoverable parameters. Major Revision starts at 01H |
| 0BH | A31:A24 | 10H | Parameter Table Length Number of DWORDs that are in the Parameter table |
| JEDEC Flash Parameter Header: 2nd DWORD | | | |
| 0CH | A7:A0 | 30H | Parameter Table Pointer (PTP) A 24-bit address that specifies the start of this header's Parameter table in the SFDP structure. The address must be DWORD-aligned. |
| 0DH | A15:A8 | 00H | |
| 0EH | A23:A16 | 00H | |
| 0FH | A31:A24 | FFH | Parameter ID Most Significant Bit (MSB) Number. |
| JEDEC Sector Map Parameter Header: 3rd DWORD | | | |
| 10H | A7:A0 | 81H | Parameter ID LSB Number. Sector Map Function-Specific Table is assigned 81H. |
| 11H | A15:A8 | 00H | Parameter Table Minor Revision Number Minor revisions are either clarifications or changes that add parameters in existing Reserved locations. Minor revisions do NOT change overall structure of SFDP. Minor Revision starts at 00H. |
| 12H | A23:A16 | 01H | Parameter Table Major Revision Number Major revisions are changes that reorganize or add parameters to locations that are NOT currently Reserved. Major revisions would require code (BIOS/firmware) or hardware change to get previously defined discoverable parameters. Major Revision starts at 01H |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (2 OF 16)

| Address | Bit Address | Data | Comments |
|--|-------------|------|--|
| 13H | A31:A24 | 06H | Parameter Table Length Number of DWORDs that are in the Parameter table |
| JEDEC Flash Parameter Header: 4th DWORD | | | |
| 14H | A7:A0 | 00H | Parameter Table Pointer (PTP) This 24-bit address specifies the start of this header's Parameter Table in the SFDP structure. The address must be DWORD-aligned. |
| 15H | A15:A8 | 01H | |
| 16H | A23:A16 | 00H | |
| 17H | A31:A24 | FFH | Parameter ID MSB. |
| Microchip (Vendor) Parameter Header: 5th DWORD | | | |
| 18H | A7:A0 | BFH | ID Number Manufacture ID (vendor specified header) |
| 19H | A15:A8 | 00H | Parameter Table Minor Revision Number |
| 1AH | A23:A16 | 01H | Parameter Table major Revision Number , Revision 1.0 |
| 1BH | A31:A24 | 18H | Parameter Table Length , 24 Double Words |
| Microchip (Vendor) Parameter Header: 6th DWORD | | | |
| 1CH | A7:A0 | 00H | Parameter Table Pointer (PTP) This 24-bit address specifies the start of this header's Parameter Table in the SFDP structure. The address must be DWORD-aligned. |
| 1DH | A15:A8 | 02H | |
| 1EH | A23:A16 | 00H | |
| 1FH | A31:A24 | 01H | Used to indicate bank number (vendor specific). |
| JEDEC Flash Parameter Table | | | |
| JEDEC Flash Parameter Table: 1st DWORD | | | |
| 30H | A1:A0 | FDH | Block/Sector Erase Sizes 00: Reserved 01: 4 KByte Erase 10: Reserved 11: Use this setting only if the 4 Byte erase is unavailable. |
| | A2 | | Write Granularity 0: Single-byte programmable devices or buffer programmable devices with buffer is less than 64 bytes (32 Words). 1: For buffer programmable devices when the buffer size is 64 bytes (32 Words) or larger. |
| | A3 | | Volatile Status Register 0: Target flash has nonvolatile status bit. Write/Erase commands do not require status register to be written on every power on. 1: Target flash has |
| | A4 | | Write Enable Opcode Select for Writing to Volatile Status Register 0: 0x50. Enables a status register write when bit 3 is set to 1. 1: 0x06 Enables a status register write when bit 3 is set to 1. |
| | A7:A5 | | Unused. Contains 111b and can not be changed |
| 31H | A15:A8 | 20H | 4 KByte Erase Opcode |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (3 OF 16)

| Address | Bit Address | Data | Comments |
|--|-------------|------|--|
| 32H | A16 | F1H | Supports (1-1-2) Fast Read 0: (1-1-2) Fast Read NOT supported 1: (1-1-2) Fast Read supported |
| | A18:A17 | | Address Bytes Number of bytes used in addressing flash array read, write and erase 00: 3-Byte only addressing 01: 3- or 4-Byte addressing (e.g. defaults to 3-Byte mode; enters 4-Byte mode on command) 10: 4-Byte only addressing 11: Reserved |
| | A19 | | Supports Double Transfer Rate (DTR) Clocking Indicates the device supports some type of double transfer rate clocking. 0: DTR NOT supported 1: DTR Clocking supported |
| | A20 | | Supports (1-2-2) Fast Read Device supports single input opcode, dual input address, and dual output data Fast Read. 0: (1-2-2) Fast Read NOT supported. 1: (1-2-2) Fast Read supported. |
| | A21 | | Supports (1-4-4) Fast Read Device supports single input opcode, quad input address, and quad output data Fast Read 0: (1-4-4) Fast Read NOT supported. 1: (1-4-4) Fast Read supported. |
| | A22 | | Supports (1-1-4) Fast Read Device supports single input opcode & address and quad output data Fast Read. 0: (1-1-4) Fast Read NOT supported. 1: (1-1-4) Fast Read supported. |
| | A23 | | Unused. Contains '1' can not be changed. |
| 33H | A31:A24 | FFH | Unused. Contains FF can not be changed |
| JEDEC Flash Parameter Table: 2nd DWORD | | | |
| 34H | A7:A0 | FFH | Flash Memory Density SST26VF016B = 00FFFFFFH |
| 35H | A15:A8 | FFH | |
| 36H | A23:A16 | FFH | |
| 37H | A31:A24 | 00H | |
| JEDEC Flash Parameter Table: 3rd DWORD | | | |
| 38H | A4:A0 | 44H | (1-4-4) Fast Read Number of Wait states (dummy clocks) needed before valid output 00100b: 4 dummy clocks (16 dummy bits) are needed with a quad input address phase instruction |
| | A7:A5 | | Quad Input Address Quad Output (1-4-4) Fast Read Number of Mode Bits 010b: 2 dummy clocks (8 mode bits) are needed with a single input opcode, quad input address and quad output data Fast Read Instruction. |
| 39H | A15:A8 | EBH | (1-4-4) Fast Read Opcode Opcode for single input opcode, quad input address, and quad output data Fast Read. |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (4 OF 16)

| Address | Bit Address | Data | Comments |
|--|-------------|------|---|
| 3AH | A20:A16 | 08H | (1-1-4) Fast Read Number of Wait states (dummy clocks) needed before valid output 01000b: 8 dummy bits are needed with a single input opcode & address and quad output data Fast Read Instruction |
| | A23:A21 | | (1-1-4) Fast Read Number of Mode Bits 000b: No mode bits are needed with a single input opcode & address and quad output data Fast Read Instruction |
| 3BH | A31:A24 | 6BH | (1-1-4) Fast Read Opcode Opcode for single input opcode & address and quad output data Fast Read. |
| JEDEC Flash Parameter Table: 4th DWORD | | | |
| 3CH | A4:A0 | 08H | (1-1-2) Fast Read Number of Wait states (dummy clocks) needed before valid output 01000b: 8 dummy clocks are needed with a single input opcode, address and dual output data fast read instruction. |
| | A7:A5 | | (1-1-2) Fast Read Number of Mode Bits 000b: No mode bits are needed with a single input opcode & address and quad output data Fast Read Instruction |
| 3DH | A15:A8 | 3BH | (1-1-2) Fast Read Opcode Opcode for single input opcode& address and dual output data Fast Read. |
| 3EH | A20:A16 | 80H | (1-2-2) Fast Read Number of Wait states (dummy clocks) needed before valid output 00010b: 0 clocks of dummy cycle. |
| | A23:A21 | | (1-2-2) Fast Read Number of Mode Bits (in clocks) 010b: 4 clocks of mode bits are needed |
| 3FH | A31:A24 | BBH | (1-2-2) Fast Read Opcode Opcode for single input opcode, dual input address, and dual output data Fast Read. |
| JEDEC Flash Parameter Table: 5th DWORD | | | |
| 40H | A0 | FEH | Supports (2-2-2) Fast Read Device supports dual input opcode& address and dual output data Fast Read. 0: (2-2-2) Fast Read NOT supported. 1: (2-2-2) Fast Read supported. |
| | A3:A1 | | Reserved. Bits default to all 1's. |
| | A4 | | Supports (4-4-4) Fast Read Device supports Quad input opcode & address and quad output data Fast Read. 0: (4-4-4) Fast Read NOT supported. 1: (4-4-4) Fast Read supported. |
| | A7:A5 | | Reserved. Bits default to all 1's. |
| 41H | A15:A8 | FFH | Reserved. Bits default to all 1's. |
| 42H | A23:A16 | FFH | Reserved. Bits default to all 1's. |
| 43H | A31:A24 | FFH | Reserved. Bits default to all 1's. |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (5 OF 16)

| Address | Bit Address | Data | Comments |
|--|-------------|------|---|
| JEDEC Flash Parameter Table: 6th DWORD | | | |
| 44H | A7:A0 | FFH | Reserved. Bits default to all 1's. |
| 45H | A15:A8 | FFH | Reserved. Bits default to all 1's. |
| 46H | A20:A16 | 00H | (2-2-2) Fast Read Number of Wait states (dummy clocks) needed before valid output 00000b: No dummy bit is needed |
| | A23:A21 | | (2-2-2) Fast Read Number of Mode Bits 000b: No mode bits are needed |
| 47H | A31:A24 | FFH | (2-2-2) Fast Read Opcode Opcode for dual input opcode& address and dual output data Fast Read. (not supported) |
| JEDEC Flash Parameter Table: 7th DWORD | | | |
| 48H | A7:A0 | FFH | Reserved. Bits default to all 1's. |
| 49H | A15:A8 | FFH | Reserved. Bits default to all 1's. |
| 4AH | A20:A16 | 44H | (4-4-4) Fast Read Number of Wait states (dummy clocks) needed before valid output 00100b: 4 clocks dummy are needed with a quad input opcode & address and quad output data Fast Read Instruction |
| | A23:A21 | | (4-4-4) Fast Read Number of Mode Bits 010b: 2 clocks mode bits are needed with a quad input opcode & address and quad output data Fast Read Instruction |
| 4BH | A31:A24 | 0BH | (4-4-4) Fast Read Opcode Opcode for quad input opcode/address, quad output data Fast Read |
| JEDEC Flash Parameter Table: 8th DWORD | | | |
| 4CH | A7:A0 | 0CH | Sector Type 1 Size 4 KByte, Sector/block size = 2 ^N bytes |
| 4DH | A15:A8 | 20H | Sector Type 1 Opcode Opcode used to erase the number of bytes specified by Sector Type 1 Size |
| 4EH | A23:A16 | 0DH | Sector Type 2 Size 8 KByte, Sector/block size = 2 ^N bytes |
| 4FH | A31:A24 | D8H | Sector Type 2 Opcode Opcode used to erase the number of bytes specified by Sector Type 2 Size |
| JEDEC Flash Parameter Table: 9th DWORD | | | |
| 50H | A7:A0 | 0FH | Sector Type 3 Size 32 KByte, Sector/block size = 2 ^N bytes |
| 51H | A15:A8 | D8H | Sector Type 3 Opcode Opcode used to erase the number of bytes specified by Sector Type 3 Size |
| 52H | A23:A16 | 10H | Sector Type 4 Size 64 KByte, Sector/block size = 2 ^N bytes |
| 53H | A31:A24 | D8H | Sector Type 4 Opcode Opcode used to erase the number of bytes specified by Sector Type 4 Size |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (6 OF 16)

| Address | Bit Address | Data | Comments |
|---|-------------|------|---|
| JEDEC Flash Parameter Table: 10th DWORD | | | |
| 54H | A3:A0 | 20H | Multiplier from typical erase time to maximum erase time Maximum time = 2*(count + 1)*Typical erase time Count = 0 A3:A0= 0000b |
| | A7:A4 | | Erase Type 1 Erase, Typical time Typical Time = (count +1)*units 1ms to 32ms, 16ms to 512ms, 128ms to 4096ms, 1s to 32s 10:9 units (00b:1ms , 01b: 16ms, 10b:128ms, 11b:1s) A8:A4 count = 18 = 10010b A10:A9 unit = 1ms = 00b |
| 55H | A10:A8 | 91H | A10:A8=001b |
| | A15:A11 | | Erase Type 2 Erase, Typical time Typical time = (count+1)*units 1ms to 32ms, 16ms to 512ms, 128ms to 4096ms, 1s to 32s 17:16 units (00b:1ms , 01b:16ms, 10b:128ms, 11b:1s) A15:A11 count = 18 =10010b A17:A16 unit = 1ms =00b |
| 56H | A17:A16 | 48H | A17:A16=00b |
| | A23:A18 | | Erase Type 3 Erase, Typical time Typical time = (count+1)*units 1ms to 32ms, 16ms to 512ms, 128ms to 4096ms, 1s to 32s 24:23 units (00b: 1ms , 01b: 16ms, 10b:128ms, 11b:1s) A22:A18 count = 18 = 10010b A24:A23 unit = 1ms = 00b |
| 57H | A24 | 24H | A24=0b |
| | A31:A25 | | Erase Type 4 Erase, Typical time Typical time = (count+1)*units 1ms to 32ms, 16ms to 512ms, 128ms to 4096ms, 1s to 32s 31:30 units (00b: 1ms , 01b: 16ms, 10b:128ms, 11b:1s) A29:A25 count=18=10010b A31:A30 unit = 1ms =00b |
| JEDEC Flash Parameter Table: 11th DWORD | | | |
| 58H | A3:A0 | 80H | Multiplier from Typical Program Time to Maximum Program Time Maximum time = 2*(count +1)*Typical program time. Count =0 A3:A0=0000b |
| | A7:A4 | | Page Size Page size = 2 ^N bytes. N=8 A7:A4 =1000b |
| 59H | A13:A8 | 6FH | Page Program Typical time Program time = (count+1)*units 13 units (0b: 8μs, 1b: 64μs) A12:A8 count=11 = 01111b A13 unit = 64μs = 1b |
| | A15:A14 | | Byte Program Typical time, first byte Typical time = (count+1)*units 18 units (0b: 1μs, 1b: 8μs) A17:A14 count = 5 = 0101b A18 =8μs=1b |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (7 OF 16)

| Address | Bit Address | Data | Comments |
|---|-------------|------|--|
| 5AH | A18:A16 | 1DH | A18:A16=101b |
| | A23:A19 | | Byte Program Typical time, Additional Byte Typical time = (count+1)*units 23 units (0b: 1µs , 1b: 8µs) A22:A19 count = 0011b A23=1µs=0b |
| 5BH | A30:A:24 | 81H | Chip Erase Typical Time Typical time = (count+1)*units 16ms to 512ms, 256ms to 8192ms, 4s to 128s, 64s to 2048s A28:A24 count =1=00001b A30:A29 units =16ms=00b |
| | A31 | | Reserved A31=1b |
| JEDEC Flash Parameter Table: 12th DWORD | | | |
| 5CH | A3:A0 | EDH | Prohibited Operations During Program Suspend xxx0b: May not initiate a new erase anywhere xxx1b: May not initiate a new erase in the program suspended page size xx0xb: May not initiate a new page program anywhere xx1xb: May not initiate a new page program in program suspended page size. x0xxb: Refer to the Data Sheet x1xxb: May not initiate a read in the program suspended page size 0xxxb: Additional erase or program restrictions apply 1xxxb: The erase and program restrictions in bits 1:0 are sufficient |
| | A7:A4 | | Prohibited Operation During Erase Suspend xxx0b: May not initiate a new erase anywhere xxx1b: May not initiate a new erase in the erase suspended page size xx0xb: May not initiate a new page program anywhere xx1xb: May not initiate a new page program in erase suspended erase type size. x0xxb: Refer to the Data Sheet x1xxb: May not initiate a read in the erase suspended page size 0xxxb: Additional erase or program restrictions apply 1xxxb: The erase and program restrictions in bits 5:4 are sufficient |
| 5DH | A8 | 0FH | Reserved = 1b |
| | A12:A9 | | Program Resume to Suspend Interval The device requires this typical amount of time to make progress on the program operation before allowing another suspend. Interval =500µs Program resume to suspend interval =(count+1)*64µs A12:A9= 7 =0111b |
| | A15:A13 | | Suspend In-progress Program Max Latency Maximum time required by the flash device to suspend an in-progress program and be ready to accept another command which accesses the flash array. Max latency = 25µs program max latency =(count+1)*units units (00b:128ns, 01b:1µs , 10b:8µs, 11b:64µs) A17:A13= count = 24 = 11000b A19:A18 = 1µs =01b |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (8 OF 16)

| Address | Bit Address | Data | Comments |
|---|-------------|------|---|
| 5EH | A19:A16 | 77H | 0111b |
| | A23:A20 | | Erase Resume to Suspend Interval The device requires this typical amount of time to make progress on the erase operation before allowing another suspend. Interval = 500µs Erase resume to suspend interval =(count+1)*64µs A23:A20= 7 = 0111b |
| 5FH | A30:A24 | 38H | Suspend In-progress Erase Max Latency Maximum time required by the flash device to suspend an in-progress erase and be ready to accept another command which accesses the flash array. Max latency = 25µs Erase max latency =(count+1)*units units (00b:128ns, 01b:1µs , 10b:8µs, 11b:64µs) A28:A24= count = 24 = 11000b A30:A29 = 1µs =01b |
| | A31 | | Suspend/Resume supported 0:supported 1:not supported |
| JEDEC Flash Parameter Table: 13th DWORD | | | |
| 60H | A7:A0 | 30H | Program Resume Instruction |
| 61H | A15:A8 | B0H | Program Suspend Instruction |
| 62H | A23:A16 | 30H | Resume Instruction |
| 63H | A31:A24 | B0H | Suspend Instruction |
| JEDEC Flash Parameter Table: 14th DWORD | | | |
| 64H | A1:A0 | F7H | Reserved = 11b |
| | A7:A2 | | Status Register Polling Device Busy 111101b: Use of legacy polling is supported by reading the status register with 05h instruction and checking WIP bit [0] (0=ready, 1=busy) |
| 65H | A14:A8 | A9H | Exit Deep Power-down to next operation delay:10µs Delay = (count+1)*unit A12:A8 = count = 9 = 01001b A14:A13 units = 01b = 1µs |
| | A15 | | Exit Power-down Instruction: ABH = 10101011b A15 = 1b |
| 66H | A22:A16 | D5H | A22:A16 = 1010101b |
| | A23 | | Enter Power-down instruction: B9H = 10111001b A23 = 1b |
| 67H | A30:A24 | 5CH | A30:A24 = 1011100 |
| | A31 | | Deep Power-down Supported 0:supported 1:not supported |
| JEDEC Flash Parameter Table: 15th DWORD | | | |
| 68H | A3:A0 | 29H | 4-4-4 Mode Disable Sequences Xxx1b: issue FF instruction 1xxx1b: issue the Soft Reset 66/99 sequence. |
| | A7:A4 | | 4-4-4 mode enable sequences X_xx1xb: issue instruction 38h |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (9 OF 16)

| Address | Bit Address | Data | Comments |
|---|-------------|------|---|
| 69H | A8 | C2H | 4-4-4 Mode Enable Sequences A8 = 0 |
| | A9 | | 0-4-4 Mode Supported 0: not supported 1: supported |
| | A15:A10 | | 0-4-4 Mode Exit Method X1_xxxx: Mode Bit[7:0] Not= AXh 1x_xxxx Reserved = 1 |
| 6AH | A19:A16 | 5CH | 0-4-4 Mode Entry Method X1xxb: M[7:0]=AXh 1xxxb: Reserved =1 |
| | A22:A20 | | Quad Enable Requirements (QER) 101b: Quad Enable is bit 1 of the configuration register. |
| | A23 | | HOLD and Reset Disable 0: feature is not supported |
| 6BH | A31:A24 | FFH | Reserved bits = 0xFF |
| JEDEC Flash Parameter Table: 16th DWORD | | | |
| 6C | A6:A0 | F0H | Volatile or Non-Volatile Register and Write Enable Instructions for Status Register 1 Xx1_xxxxb: Status Register 1 contains a mix of volatile and non-volatile bits. The 06h instruction is used to enable writing to the register. X1x_xxxxb: Reserved = 1 1xx_xxxxb: Reserved = 1 |
| | A7 | | Reserved =1b |
| 6D | A13:A8 | 30H | Soft Reset and Rescue Sequence Support X1_xxxxb: reset enable instruction 66h is issued followed by reset instruction 99h. 1x_xxxxb: exit 0-4-4 mode is required prior to other reset sequences. |
| | A15:A14 | | Exit 4-Byte Addressing Not supported |
| 6E | A23:A16 | C0H | Exit 4-Byte Addressing Not supported A21:A14 = 000000b A23 and A22 are Reserved bits which are = 1 |
| 6F | A31:A24 | 80H | Enter 4-Byte Addressing Not supported 1xxx_xxxx: Reserved = 1 |
| JEDEC Sector Map Parameter Table | | | |
| 100H | A7:A0 | FFH | Sector Map A7:A2=Reserved=111111b A1=Descriptor Type = Map=1b A0=Last map = 1b |
| 101H | A15:A8 | 00H | Configuration ID = 00h |
| 102H | A23:A16 | 04H | Region Count = 5 Regions |
| 103H | A31:A24 | FFH | Reserved = FFH |
| 104H | A7:A0 | F3H | Region 0 supports 4 KByte erase and 8 KByte erase A3:A0=0011b A7:A4=Reserved=1111b |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (10 OF 16)

| Address | Bit Address | Data | Comments |
|---------|-------------|------|---|
| 105H | A15:A8 | 7FH | Region 0 Size 4 * 8 KBytes = 32 KBytes Count=32 KBytes/256 Bytes= 128 Value = count -1 =127 A31:A8 = 00007Fh |
| 106H | A23:A16 | 00H | |
| 107H | A31:A24 | 00H | |
| 108H | A7:A0 | F5H | Region 1 supports 4 KByte erase and 32 KByte erase A3:A0 = 0101b A7:A4=Reserved = 1111b |
| 109H | A15:A8 | 7FH | Region 1 size 1 * 32Kbytes = 32Kbytes Count=32Kbytes/256 bytes= 128 Value = count -1 =127 A31:A8 = 00007Fh |
| 10AH | A23:A16 | 00H | |
| 10BH | A31:A24 | 00H | |
| 10CH | A7:A0 | F9H | Region 2 supports 4 KByte erase and 64 KByte erase A3:A0 = 1001b A7:A4=Reserved = 1111b |
| 10DH | A15:A8 | FFH | Region 2 size 30 * 64 KBytes = 1920 KBytes Count=1920 KBytes/256 Bytes= 7680 Value = count -1 =7679 A31:A8 = 001DFFh |
| 10EH | A23:A16 | 1DH | |
| 10FH | A31:A24 | 00H | |
| 110H | A7:A0 | F5H | Region 3 supports 4 KByte erase and 32 KByte erase A3:A0 = 0101b A7:A4=Reserved = 1111b |
| 111H | A15:A8 | 7FH | Region 3 size 1 * 32 KBytes = 32 KBytes Count=32 KBytes/256 bytes= 128 Value = count -1 =127 A31:A8 = 00007Fh |
| 112H | A23:A16 | 00H | |
| 113H | A31:A24 | 00H | |
| 114H | A7:A0 | F3H | Region 4 supports 4 KByte erase and 8 KByte erase A3:A0=0011b A7:A4=Reserved=1111b |
| 115H | A15:A8 | 7FH | Region 4 Size 4 * 8 KBytes = 32 KBytes Count=32 KBytes/256 bytes= 128 Value = count -1 =127 A31:A8 = 00007Fh |
| 116H | A23:A16 | 00H | |
| 117H | A31:A24 | 00H | |

SST26VF016B

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (11 OF 16)

| Address | Bit Address | Data | Comments |
|---|-------------|------|---|
| SST26VF016B (Vendor) Parameter Table | | | |
| SST26VF016B Identification | | | |
| 200H | A7:A0 | BFH | Manufacturer ID |
| 201H | A15:A8 | 26H | Memory Type |
| 202H | A23:A16 | 41H | Device ID SST26VF016B=41H |
| 203H | A31:A24 | FFH | Reserved. Bits default to all 1's. |
| SST26VF016B Interface | | | |
| 204H | A2:A0 | B9H | Interfaces Supported 000: SPI only 001: Power up default is SPI; Quad can be enabled/disabled 010: Reserved : : 111: Reserved |
| | A3 | | Supports Enable Quad 0: not supported 1: supported |
| | A6:A4 | | Supports Hold#/Reset# Function 000: Hold# 001: Reset# 010: HOLD/Reset# 011: Hold# & I/O when in SQI(4-4-4), 1-4-4 or 1-1-4 Read |
| | A7 | | Supports Software Reset 0: not supported 1: supported |
| 205H | A8 | DFH | Supports Quad Reset 0: not supported 1: supported |
| | A10:A9 | | Reserved. Bits default to all 1's |
| | A13:A11 | | Byte-Program or Page-Program (256 Bytes) 011: Byte Program/Page Program in SPI and Quad Page Program once Quad is enabled |
| | A14 | | Program-Erase Suspend Supported 0: Not Supported 1: Program/Erase Suspend Supported |
| | A15 | | Deep Power-Down Mode Supported 0: Not Supported 1: Deep Power-Down Mode Supported |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (12 OF 16)

| Address | Bit Address | Data | Comments |
|---------|-------------|------|--|
| 206H | A16 | FDH | OTP Capable (Security ID) Supported 0: not supported 1: supported |
| | A17 | | Supports Block Group Protect 0: not supported 1: supported |
| | A18 | | Supports Independent Block Protect 0: not supported 1: supported |
| | A19 | | Supports Independent non Volatile Lock (Block or Sector becomes OTP) 0: not supported 1: supported |
| | A23:A20 | | Reserved. Bits default to all 1's. |
| 207H | A31:A24 | FFH | Reserved. Bits default to all 1's. |
| 208H | A7:A0 | 30H | V_{DD} Minimum Supply Voltage 2.3V (F230H) |
| 209H | A15:A8 | F2H | |
| 20AH | A23:A16 | 60H | V_{DD} Maximum Supply Voltage 3.6V (F360H) |
| 20BH | A31:A24 | F3H | |
| 20CH | A7:A0 | 32H | Typical time out for Byte-Program: 50 μs Typical time out for Byte Program is in μs. Represented by conversion of the actual time from the decimal to hexadecimal number. |
| 20DH | A15:A8 | FFH | Reserved. Bits default to all 1's. |
| 20EH | A23:A16 | 0AH | Typ time out for page program: 1.0ms (xxH*(0.1ms)) |
| 20FH | A31:A24 | 12H | Typical time out for Sector-Erase/Block-Erase: 18 ms Typical time out for Sector/Block-Erase is in ms. Represented by conversion of the actual time from the decimal to hexadecimal number. |
| 210H | A7:A0 | 23H | Typical time out for Chip-Erase: 35 ms Typical time out for Chip-Erase is in ms. Represented by conversion of the actual time from the decimal to hexadecimal number. |
| 211H | A15:A8 | 46H | Max. time out for Byte-Program: 70 μs Typical time out for Byte Program is in μs. Represented by conversion of the actual time from the decimal to hexadecimal number. |
| 212H | A23:A16 | FFH | Reserved. Bits default to all 1's. |
| 213H | A31:A24 | 0FH | Max time out for Page-Program: 1.5ms. Typical time out for Page Program in xxH * (0.1ms) ms |
| 214H | A7:A0 | 19H | Max. time out for Sector Erase/Block Erase: 25ms. Max time out for Sector/Block Erase in ms |
| 215H | A15:A8 | 32H | Max. time out for Chip Erase: 50ms. Max time out for Chip Erase in ms. |
| 216H | A23:A16 | 0FH | Max. time out for Program Security ID: 1.5 ms Max time out for Program Security ID in xxH*(0.1ms) ms |
| 217H | A31:A24 | 19H | Max. time out for Write-Protection Enable Latency: 25 ms Max time out for Write-Protection Enable Latency is in ms. Represented by conversion of the actual time from the decimal to hexadecimal number. |
| 218H | A23:A16 | 19H | Max. time Write-Suspend Latency: 25 μs Max time out for Write-Suspend Latency is in μs. Represented by conversion of the actual time from the decimal to hexadecimal number. |
| 219H | A31:A24 | 03H | Max. time to Deep Power-Down: 3μs = 03H) |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (13 OF 16)

| Address | Bit Address | Data | Comments |
|-------------------------------|-------------|------|--|
| 21AH | A23:A16 | 0AH | Max. time out from Deep Power-Down mode to Standby mode: 10 μ s = 0AH |
| 21BH | A31:A24 | FFH | Reserved. Bits default to all 1's. |
| 21CH | A23:A16 | FFH | Reserved. Bits default to all 1's. |
| 21DH | A31:A24 | FFH | Reserved. Bits default to all 1's. |
| 21EH | A23:A16 | FFH | Reserved. Bits default to all 1's. |
| 21FH | A31:A24 | FFH | Reserved. Bits default to all 1's. |
| Supported Instructions | | | |
| 220H | A7:A0 | 00H | No Operation |
| 221H | A15:A8 | 66H | Reset Enable |
| 222H | A23:A16 | 99H | Reset Memory |
| 223H | A31:A24 | 38H | Enable Quad I/O |
| 224H | A7:A0 | FFH | Reset Quad I/O |
| 225H | A15:A8 | 05H | Read Status Register |
| 226H | A23:A16 | 01H | Write Status Register |
| 227H | A31:A24 | 35H | Read Configuration Register |
| 228H | A7:A0 | 06H | Write Enable |
| 229H | A15:A8 | 04H | Write Disable |
| 22AH | A23:A16 | 02H | Byte Program or Page Program |
| 22BH | A31:A24 | 32H | SPI Quad Page Program |
| 22CH | A7:A0 | B0H | Suspends Program/Erase |
| 22DH | A15:A8 | 30H | Resumes Program/Erase |
| 22EH | A23:A16 | 72H | Read Block-Protection register |
| 22FH | A31:A24 | 42H | Write Block Protection Register |
| 230H | A7:A0 | 8DH | Lock Down Block Protection Register |
| 231H | A15:A8 | E8H | non-Volatile Write-Lock Down Register |
| 232H | A23:A16 | 98H | Global Block Protection Unlock |
| 233H | A31:A24 | 88H | Read Security ID |
| 234H | A7:A0 | A5H | Program User Security ID Area |
| 235H | A15:A8 | 85H | Lockout Security ID Programming |
| 236H | A23:A16 | C0H | Set Burst Length |
| 237H | A31:A24 | 9FH | JEDEC-ID |
| 238H | A7:A0 | AFH | Quad J-ID |
| 239H | A15:A8 | 5AH | SFDP |
| 23AH | A23:A16 | B9H | Deep Power-Down Mode |
| 23BH | A31:A24 | ABH | Release Deep Power-Down Mode |
| 23CH | A4:A0 | 06H | (1-4-4) SPI nB Burst with Wrap Number of Wait states (dummy clocks) needed before valid output 00110b: 6 clocks of dummy cycle |
| | A7:A5 | | (1-4-4) SPI nB Burst with Wrap Number of Mode Bits 000b: Set Mode bits are not supported |
| 23DH | A15:A8 | ECH | (1-4-4) SPI nB Burst with Wrap Opcode |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (14 OF 16)

| Address | Bit Address | Data | Comments | |
|--|---------------|------|---|--|
| 23EH | A20:A16 | 06H | (4-4-4) SQI nB Burst with Wrap Number of Wait states (dummy clocks) needed before valid output 00110b: 6 clocks of dummy cycle | |
| | A23:A21 | | (4-4-4) SQI nB Burst with Wrap Number of Mode Bits 000b: Set Mode bits are not supported | |
| 23FH | A31:A24 | 0CH | (4-4-4) SQI nB Burst with Wrap Opcode | |
| 240H | A4:A0 | 00H | (1-1-1) Read Memory Number of Wait states (dummy clocks) needed before valid output 00000b: Wait states/dummy clocks are not supported. | |
| | A7:A5 | | (1-1-1) Read Memory Number of Mode Bits 000b: Mode bits are not supported, | |
| 241H | A15:A8 | 03H | (1-1-1) Read Memory Opcode | |
| 242H | A20:A16 | 08H | (1-1-1) Read Memory at Higher Speed Number of Wait states (dummy clocks) needed before valid output 01000: 8 clocks (8 bits) of dummy cycle | |
| | A23:A21 | | (1-1-1) Read Memory at Higher Speed Number of Mode Bits 000b: Mode bits are not supported, | |
| 243H | A31:A24 | 0BH | (1-1-1) Read Memory at Higher Speed Opcode | |
| 244H | A7:A0 | FFH | Reserved. Bits default to all 1's. | |
| 245H | A15:A8 | FFH | Reserved. Bits default to all 1's. | |
| 246H | A23:A16 | FFH | Reserved. Bits default to all 1's. | |
| 247H | A31:A24 | FFH | Reserved. Bits default to all 1's. | |
| Security ID | | | | |
| 248H | A7:A0 | FFH | Security ID size in bytes Example: If the size is 2 KBytes, this field would be 07FFH | |
| 249H | A15:A8 | 07H | Security ID Range | |
| | | | <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 60%;">Unique ID (Pre-programmed at factory)</td> <td style="width: 40%;">0000H - 0007H</td> </tr> <tr> <td>User Programmable</td> <td>0008H - 07FFH</td> </tr> </table> | Unique ID (Pre-programmed at factory) |
| Unique ID (Pre-programmed at factory) | 0000H - 0007H | | | |
| User Programmable | 0008H - 07FFH | | | |
| 24AH | A23:A16 | FFH | Reserved. Bits default to all 1's. | |
| 24BH | A31:A24 | FFH | Reserved. Bits default to all 1's. | |
| Memory Organization/Block Protection Bit Mapping ¹ | | | | |
| 24CH | A7:A0 | 02H | Section 1: Sector Type Number: Sector type in JEDEC Parameter Table (bottom, 8 KByte) | |
| 24DH | A15:A8 | 02H | Section 1 Number of Sectors Four of 8KB block (2^n) | |
| 24EH | A23:A16 | FFH | Section 1 Block Protection Bit Start $((2^m) + 1) + c$, $c = \text{FFH}$ or -1 , $m = 5$ for 16Mb Address bits are Read Lock bit locations and Even Address bits are Write Lock bit locations. The most significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative. | |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (15 OF 16)

| Address | Bit Address | Data | Comments |
|---------|-------------|------|--|
| 24FH | A31:A24 | 06H | Section 1 (bottom) Block Protection Bit End $((2^m) + 1) + c$, c=06H or 6, m= 5 for 16Mb Address bits are Read Lock bit locations and Even Address bits are Write Lock bit locations. The most significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative. |
| 250H | A7:A0 | 03H | Section 2: Sector Type Number Sector type in JEDEC Parameter Table (32KB Block) |
| 251H | A15:A8 | 00H | Section 2 Number of Sectors One of 32KB Block (2^n , n=0) |
| 252H | A23:A16 | FDH | Section 2 Block Protection Bit Start $((2^m) + 1) + c$, c=FDH or -3, m= 5 for 16Mb The most significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative. |
| 253H | A31:A24 | FDH | Section 2 Block Protection Bit End $((2^m) + 1) + c$, c=FDH or -3, m= 5 for 16Mb The most significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative. |
| 254H | A7:A0 | 04H | Section 3: Sector Type Number Sector type in JEDEC Parameter Table (64KB Block) |
| 255H | A15:A8 | 05H | Section 3 Number of Sectors 126 of 64KB Block ($2^n - 2$, n= 5 for 16Mb) |
| 256H | A23:A16 | 00H | Section 3 Block Protection Bit Start Section 3 Block Protection Bit starts at 00H |
| 257H | A31:A24 | FCH | Section 3 Block Protection Bit End $((2^m) + 1) + c$, c=FCH or -4, m= 5 for 16Mb |
| 258H | A7:A0 | 03H | Section 4: Sector Type Number Sector type in JEDEC Parameter Table (32KB Block) |
| 259H | A15:A8 | 00H | Section 4 Number of Sectors One of 32KB Block (2^n , n=0) |
| 25AH | A23:A16 | FEH | Section 4 Block Protection Bit Start $((2^m) + 1) + c$, c=FEH or -2, m= 5 for 16Mb The most significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative. |
| 25BH | A31:A24 | FEH | Section 4 Block Protection Bit End $((2^m) + 1) + c$, c=FEH or -2, m= 5 for 16Mb The most significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative. |
| 25CH | A7:A0 | 02H | Section 5 Sector Type Number: Sector type in JEDEC Parameter Table (top, 8 KByte) |
| 25DH | A15:A8 | 02H | Section 5 Number of Sectors Four of 8KB block (2^n) |

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (16 OF 16)

| Address | Bit Address | Data | Comments |
|---------|-------------|------|--|
| 25EH | A23:A16 | 07H | Section 5 Block Protection Bit Start $((2^m) + 1) + c$, $c=07H$ or 7 , $m= 5$ for 16Mb Address bits are Read Lock bit locations and Even Address bits are Write Lock bit locations. The most significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative. |
| 25FH | A31:A24 | 0EH | Section 5 (bottom) Block Protection Bit End $((2^m) + 1) + c$, $c=0EH$ or 14 , $m= 5$ for 16Mb Address bits are Read Lock bit locations and Even Address bits are Write Lock bit locations. The most significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative. |

1. See "Mapping Guidance Details" for more detailed mapping information

11.1 Mapping Guidance Details

The SFDP Memory Organization/Block Protection Bit Mapping defines the memory organization including uniform sector/block sizes and different contiguous sectors/blocks sizes. In addition, this bit defines the

number of these uniform and different sectors/blocks from address 000000H to the full range of Memory and the associated Block Locking Register bits of each sector/block.

Each major Section is defined as follows:

TABLE 11-2: SECTION DEFINITION

| | |
|-----------------|---|
| Major Section X | Section X: Sector Type Number |
| | Section X: Number of Sectors |
| | Section X: Block-Protection Register Bit Start Location |
| | Section X: Block-Protection Register Bit End Location |

A Major Section consists of Sector Type Number, Number of Sector of this type, and the Block-Protection Bit Start/End locations. This is tied directly to JEDEC Flash Parameter Table Sector Size Type (in 7th DWORD and 8th DWORD section). Note that the contiguous 4KByte Sectors across the full memory range are not included on this section because they are not defined in the JEDEC Flash Parameter Table Sector Size Type section. Only the sectors/blocks that are dependently tied with the Block-Protection Register bits are defined. A major section is a partition of contiguous same-size sectors/blocks. There will be several Major Sections as you dissect across memory from 000000h to the full range. Similar sector/block size that re-appear may be defined as a different Major Section.

located at address location 52H. Contiguous Same Sector Type # Size can re-emerge across the memory range and this Sector Type # will indicate that it is a separate/independent Major Section from the previous contiguous sectors/blocks.

11.1.1 SECTOR TYPE NUMBER

Sector Type Number is the sector/block size typed defined in JEDEC Flash Parameter Table: SFDP address locations 4CH, 4EH, 50H and 52H. Sector Type 1, which is represented by 01H, is located at address 4CH. Sector Type 2, which is represented by 02H, is located at address location 4EH. Sector Type 3, which is represented by 03H, is located at address location 50H. Sector Type 4, represented by 04H, is

11.1.2 NUMBER OF SECTORS

Number of Sectors represents the number of contiguous sectors/blocks with similar size. A formula calculates the contiguous sectors/blocks with similar size. Given the sector/block size, type, and the number of sectors, the address range of these sectors/blocks can be determined along with specific Block Locking Register bits that control the read/write protection of each sectors/blocks.

11.1.3 BLOCK-PROTECTION REGISTER BIT START LOCATION (BPSL)

Block-Protection Register Bit Start Location (BPSL) designates the start bit location in the Block-Protection Register where the first sector/block of this Major Section begins. If the value of BPSL is 00H, this location is

the 0 bit location. If the value is other than 0, then this value is a constant value adder (c) for a given formula, $(2^m + 1) + (c)$. See “Memory Configuration”.

From the initial location, there will be a bit location for every increment by 1 until it reaches the Block Protection Register Bit End Location (BPEL). This number range from BPSL to BPEL will correspond to, and be equal to, the number of sectors/blocks on this Major Section.

11.1.4 BLOCK PROTECTION REGISTER BIT END LOCATION (BPEL)

Block Protection Register Bit End Location designates the end bit location in the Block Protection Register bit where the last sector/block of this Major Section ends.

The value in this field is a constant value adder (c) for a given formula or equation, $(2^m + 1) + (c)$. See “Memory Configuration”

11.1.5 MEMORY CONFIGURATION

For the SST26VF016B family, the memory configuration is setup with different contiguous block sizes from bottom to the top of the memory. For example, starting from bottom of memory it has four 8KByte blocks, one 32KByte block, x number of 64KByte blocks depending on memory size, then one 32KByte block, and four 8KByte block on the top of memory. See [Table 11-3](#).

TABLE 11-3: MEMORY BLOCK DIAGRAM REPRESENTATION

| | |
|--|---|
| 8 KByte Bottom Block (from 000000H) | Section 1: Sector Type Number |
| | Section 1: Number of Sectors |
| | Section 1: Block-Protection Register Bit Start Location |
| | Section 1: Block-Protection Register Bit End Location |
| 32 KByte | Section 2: Sector Type Number |
| | Section 2: Number of Sectors |
| | Section 2: Block-Protection Register Bit Start Location |
| | Section 2: Block-Protection Register Bit End Location |
| 64 KByte | Section 3: Sector Type Number |
| | Section 3: Number of Sectors |
| | Section 3: Block-Protection Register Bit Start Location |
| | Section 3: Block-Protection Register Bit End Location |
| 32 KByte | Section 4: Sector Type Number |
| | Section 4: Number of Sectors |
| | Section 4: Block-Protection Register Bit Start Location |
| | Section 4: Block-Protection Register Bit End Location |
| 8 KByte (Top Block) | Section 5: Sector Type Number |
| | Section 5: Number of Sectors |
| | Section 5: Block-Protection Register Bit Start Location |
| | Section 5: Block-Protection Register Bit End Location |

Classifying these sector/block sizes via the Sector Type derived from JEDEC Flash Parameter Table: SFDP address locations 4EH, 50H, and 52His as follows:

- 8 KByte Blocks are classified as Sector Type 2 (@4EH of SFDP)
- 32 KByte Blocks are classified as Sector Type 3 (@50H of SFDP)
- 64 KByte Blocks are classified as Sector Type 4 (@52H of SFDP)

m will have a constant value for specific densities and

For the Number of Sectors associated with the contiguous sectors/blocks, a formula is used to determine the number of sectors/blocks of these Sector Types:

- 8KByte Block (Type 2) is calculated by 2^n . n is a byte.
- 32KByte Block (Type 3) is calculated by 2^n . n is a byte.
- 64KByte Block (Type 4) is calculated by $(2^m - 2)$. m can either be a 4, 5, 6, 7 or 8 depending on the memory size. This m field is going to be used for the 64KByte Block Section and will also be used for the Block Protection Register Bit Location formula.

is defined as:

- 8Mbit = 4
- 16Mbit = 5
- 32Mbit = 6
- 64Mbit = 7
- 128Mbit = 8

Block Protect Register Start/End Bits are mapped in the SFDP by using the formula $(2^m + 1) + (c)$. "m" is a constant value that represents the different densities from 8Mbit to 128Mbit (used also in the formula calculating number of 64Kbyte Blocks above). The values that are going to be placed in the Block Protection Bit Start/End

field table are the constant value adder (c) in the formula and are represented in two's complement except when the value is 00H. If the value is 00H, this location is the 0 bit location. If the value is other than 0, then this is a constant value adder (c) that will be used in the formula. The most significant (left most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one, then the number is less than zero, or negative.

See [Table 11-4](#) for an example of this formula.

TABLE 11-4: BPSL/BPEL EQUATION WITH ACTUAL CONSTANT ADDER DERIVED FROM THE FORMULA $(2^M + 1) + (C)$

| Block Size | 8 Mbit to 128 Mbit | Comments |
|-------------------------|---|--|
| 8 KByte (Type 2) Bottom | BPSL = $(2^m + 1) + 0FFH$ BPEL = $(2^m + 1) + 04H$ | 0FFH = -1; 06H = 6 Odd address bits are Read-Lock bit locations and even address bits are Write-Lock bit locations. |
| 32 KByte (Type3) | BPSL = BPEL= $(2^m + 1) + 0FDH$ | 0FDH= -3 |
| 64 KByte (Type 4) | BPSL = 00H BPEL = $(2^m + 1) + 0FCH$ | 00H is Block-Protection Register bit 0 location; 0FCH = -4 |
| 32 KByte (Type 3) | BPSL = BPEL= $(2^m + 1) + 0FEH$ | 0FEH=-2 |
| 8 KByte (Type 2) Top | BPSL = $(2^m + 1) + 07H$ BPEL = $(2^m + 1) + 0EH$ | 07H = 7; 0EH = 14 Odd address bits are Read-Lock bit locations and even address bits are Write-Lock bit locations. |

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